# Eduardo Alves

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/7484251/publications.pdf

Version: 2024-02-01

| 785 | 13,721 | 34016 | 69108 |
|---|---|---|---|
| papers | citations | 52 h-index | 77 g-index |

| 794 | 794 | 794 | 10761 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Overview of JET results for optimising ITER operation. Nuclear Fusion, 2022, 62, 042026. | 1.6 | 52 |
| 2 | Improvement of Mechanical Properties with Non-Equimolar CrNbTaVW High Entropy Alloy. Crystals, 2022, 12, 219. | 1.0 | 4 |
| 3 | Structural analysis of the ZnO/MgO superlattices on a-polar ZnO substrates grown by MBE. Applied Surface Science, 2022, 587, 152830. | 3.1 | 3 |
| 4 | Tantalum-Titanium Oxynitride Thin Films Deposited by DC Reactive Magnetron Co-Sputtering: Mechanical, Optical, and Electrical Characterization. Coatings, 2022, 12, 36. | 1.2 | 6 |
| 5 | Confronting Vegardâ€™s rule in Ge<sub>1â^'x </sub>Sn <sub>x</sub> epilayers: from fundamentals to the effect of defects. Journal Physics D: Applied Physics, 2022, 55, 295301. | 1.3 | 2 |
| 6 | Enhancing the luminescence yield of Cr3+ in  Î² -Ga2O3 by proton irradiation. Applied Physics Letters, 2022, 120, . | 1.5 | 8 |
| 7 | Dependence of optical properties on composition of silicon carbonitride thin films deposited at low temperature by PECVD. Journal of Non-Crystalline Solids, 2021, 551, 120434. | 1.5 | 7 |
| 8 | Microwave transient reflection in annealed SnS thin films. Materials Science in Semiconductor Processing, 2021, 121, 105302. | 1.9 | 5 |
| 9 | The effects of mechanical alloying on the physical and thermal properties of CuCrFeTiV alloy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2021, 263, 114805. | 1.7 | 5 |
| 10 | Ion beam analysis of Li-Sn alloys for fusion applications. Nuclear Instruments & Methods in Physics Research B, 2021, 486, 55-62. | 0.6 | 0 |
| 11 | Deposition of Ti-Zr-O-N films by reactive magnetron sputtering of Zr target with Ti ribbons. Surface and Coatings Technology, 2021, 409, 126737. | 2.2 | 3 |
| 12 | Electrical, optical and photoconductive properties of Sn-doped indium sulfofluoride thin films. Materials Science in Semiconductor Processing, 2021, 121, 105349. | 1.9 | 1 |
| 13 | Crystal mosaicity determined by a novel layer deconvolution Williamsonâ€“Hall method. CrystEngComm, 2021, 23, 2048-2062. | 1.3 | 8 |
| 14 | Multiple reflection optimization package for X-ray diffraction. CrystEngComm, 2021, 23, 3308-3318. | 1.3 | 6 |
| 15 | Eu3+ optical activation engineering in Al Ga1-N nanowires for red solid-state nano-emitters. Applied Materials Today, 2021, 22, 100893. | 2.3 | 4 |
| 16 | Unravelling the secrets of the resistance of GaN to strongly ionising radiation. Communications Physics, 2021, 4, . | 2.0 | 26 |
| 17 | Simulating the effect of Ar+ energy implantation on the strain propagation in AlGaN. Journal Physics D: Applied Physics, 2021, 54, 245301. | 1.3 | 6 |
| 18 | Self-powered proton detectors based on GaN coreâ€“shell pâ€“n microwires. Applied Physics Letters, 2021, 118, . | 1.5 | 3 |

| # | Article | IF | Citations |
|---|---|---|---|
| 19 | An insider view of the Portuguese ion beam laboratory. European Physical Journal Plus, 2021, 136, 1. | 1.2 | 15 |
| 20 | Use of a Timepix position-sensitive detector for Rutherford backscattering spectrometry with channeling. Nuclear Instruments & Methods in Physics Research B, 2021, 499, 61-69. | 0.6 | 2 |
| 21 | Enhanced red emission from Eu-implanted ZnMgO layers and ZnO/ZnMgO quantum structures. Applied Physics Letters, 2021, 119, . | 1.5 | 4 |
| 22 | Nonpolar short-period ZnO/MgO superlattices: Radiative excitons analysis. Journal of Luminescence, 2021, 238, 118288. | 1.5 | 4 |
| 23 | In-situ annealing transmission electron microscopy of plasmonic thin films composed of bimetallic Auâ€“Ag nanoparticles dispersed in a TiO2 matrix. Vacuum, 2021, 193, 110511. | 1.6 | 8 |
| 24 | Ta2O5/SiO2 Multicomponent Dielectrics for Amorphous Oxide TFTs. Electronic Materials, 2021, 2, 1-16. | 0.9 | 6 |
| 25 | Fuel retention and erosion-deposition on inner wall cladding tiles in JET-ILW. Physica Scripta, 2021, 96, 124071. | 1.2 | 7 |
| 26 | Evaluation of tritium retention in plasma facing components during JET tritium operations. Physica Scripta, 2021, 96, 124075. | 1.2 | 14 |
| 27 | Me-Doped Tiâ€“Me Intermetallic Thin Films Used for Dry Biopotential Electrodes: A Comparative Case Study. Sensors, 2021, 21, 8143. | 2.1 | 5 |
| 28 | Thin films of Au-Al2O3 for plasmonic sensing. Applied Surface Science, 2020, 500, 144035. | 3.1 | 13 |
| 29 | Evolution of the mechanical properties of Ti-based intermetallic thin films doped with different metals to be used as biomedical devices. Applied Surface Science, 2020, 505, 144617. | 3.1 | 22 |
| 30 | Deuterium inventory determination in beryllium and mixed beryllium-carbon layers doped with oxygen. Fusion Engineering and Design, 2020, 150, 111365. | 1.0 | 4 |
| 31 | Ion beam analysis of fusion plasma-facing materials and components: facilities and research challenges. Nuclear Fusion, 2020, 60, 025001. | 1.6 | 54 |
| 32 | Estimating the uncertainties of strain and damage analysis by X-ray diffraction in ion implanted MoO3. Nuclear Instruments & Methods in Physics Research B, 2020, 478, 290-296. | 0.6 | 1 |
| 33 | Lithium dilution in Li-Sn alloys. Nuclear Materials and Energy, 2020, 25, 100783. | 0.6 | 4 |
| 34 | Ion beam induced current analysis in GaN microwires. EPJ Web of Conferences, 2020, 233, 05001. | 0.1 | 1 |
| 35 | Nanostructured c-Si surfaces obtained by sequential ion implantation of C+ and Ti+: Tribophysical and structural characterization. Nuclear Instruments & Methods in Physics Research B, 2020, 471, 69-75. | 0.6 | 0 |
| 36 | Stopping power of hydrogen in hafnium and the importance of relativistic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>4</mml:mn><mml:mi>f</mml:mi><mml:mrow></mml:m electrons. Physical Review A, 2020, 101, . | 1.0 | 8 |

| # | Article | IF | Citations |
|---|---|---|---|
| 37 | Post-mortem analysis of tungsten plasma facing components in tokamaks: Raman microscopy measurements on compact, porous oxide and nitride films and nanoparticles. Nuclear Fusion, 2020, 60, 086004. | 1.6 | 10 |
| 38 | Oxidation behaviour of neutron irradiated Be pebbles. Nuclear Materials and Energy, 2020, 23, 100748. | 0.6 | 3 |
| 39 | Fuel inventory and material migration of JET main chamber plasma facing components compared over three operational periods. Physica Scripta, 2020, T171, 014051. | 1.2 | 20 |
| 40 | Deposition in the tungsten divertor during the 2011â€“2016 campaigns in JET with ITER-like wall. Physica Scripta, 2020, T171, 014044. | 1.2 | 11 |
| 41 | Effect of composition and surface characteristics on fuel retention in beryllium-containing co-deposited layers. Physica Scripta, 2020, T171, 014038. | 1.2 | 12 |
| 42 | Ar<sup>+</sup> ion irradiation of magnetic tunnel junction multilayers: impact on the magnetic and electrical properties. Journal Physics D: Applied Physics, 2020, 53, 455003. | 1.3 | 6 |
| 43 | W/AlSiTiNx/SiAlTiOyNx/SiAlOx multilayered solar thermal selective absorber coating. Solar Energy, 2020, 207, 192-198. | 2.9 | 18 |
| 44 | Study of structural and optical properties of MBE grown nonpolar (10-10) ZnO/ZnMgO photonic structures. Optical Materials, 2020, 100, 109709. | 1.7 | 8 |
| 45 | Nanocomposite Au-ZnO thin films: Influence of gold concentration and thermal annealing on the microstructure and plasmonic response. Surface and Coatings Technology, 2020, 385, 125379. | 2.2 | 8 |
| 46 | Advanced Monte Carlo Simulations for Ion-Channeling Studies of Complex Defects in Crystals. Springer Series in Materials Science, 2020, , 133-160. | 0.4 | 3 |
| 47 | Photoelectrochemical Water Splitting: Thermal Annealing Challenges on Hematite Nanowires. Journal of Physical Chemistry C, 2020, 124, 12897-12911. | 1.5 | 24 |
| 48 | Deuterium retention on the tungsten-coated divertor tiles of JET ITER-like wall in 2015â€“2016 campaign. Fusion Engineering and Design, 2019, 146, 1979-1982. | 1.0 | 5 |
| 49 | Micro-Opto-Electro-Mechanical Device Based on Flexible Î²-Ga<sub>2</sub>O<sub>3</sub>ÂMicro-Lamellas. ECS Journal of Solid State Science and Technology, 2019, 8, Q3235-Q3241. | 0.9 | 3 |
| 50 | Structural and optical studies of aluminosilicate films doped with (Tb3+, Er3+)/Yb3+ by ion implantation. Nuclear Instruments & Methods in Physics Research B, 2019, 459, 71-75. | 0.6 | 4 |
| 51 | Metallic filamentary conduction in valence change-based resistive switching devices: the case of TaO<sub>x</sub> thin film with x â‰¤ 1. Nanoscale, 2019, 11, 16978-16990. | 2.8 | 16 |
| 52 | Overview of the JET preparation for deuteriumâ€“tritium operation with the ITER like-wall. Nuclear Fusion, 2019, 59, 112021. | 1.6 | 87 |
| 53 | Direct observation of mono-vacancy and self-interstitial recovery in tungsten. APL Materials, 2019, 7, . | 2.2 | 45 |
| 54 | New WC-Cu composites for the divertor in fusion reactors. Journal of Nuclear Materials, 2019, 521, 31-37. | 1.3 | 12 |

| # | Article | IF | Citations |
|---|---|---|---|
| 55 | Measuring strain caused by ion implantation in GaN. Materials Science in Semiconductor Processing, 2019, 98, 95-99. | 1.9 | 15 |
| 56 | Luminescence properties of MOCVD grown Al0.2Ga0.8N layers implanted with Tb. Journal of Luminescence, 2019, 210, 413-424. | 1.5 | 1 |
| 57 | Deposition of impurity metals during campaigns with the JET ITER-like Wall. Nuclear Materials and Energy, 2019, 19, 218-224. | 0.6 | 23 |
| 58 | Stability of beryllium coatings deposited on carbon under annealing up to 1073 K. Fusion Engineering and Design, 2019, 146, 303-307. | 1.0 | 4 |
| 59 | Thin films composed of metal nanoparticles (Au, Ag, Cu) dispersed in AlN: The influence of composition and thermal annealing on the structure and plasmonic response. Thin Solid Films, 2019, 676, 12-25. | 0.8 | 20 |
| 60 | The effect of increasing Si content in the absorber layers (CrAlSiNx/CrAlSiOyNx) of solar selective absorbers upon their selectivity and thermal stability. Applied Surface Science, 2019, 481, 1096-1102. | 3.1 | 7 |
| 61 | First mirror test in JET for ITER: Complete overview after three ILW campaigns. Nuclear Materials and Energy, 2019, 19, 59-66. | 0.6 | 24 |
| 62 | Tritium distributions on W-coated divertor tiles used in the third JET ITER-like wall campaign. Nuclear Materials and Energy, 2019, 18, 258-261. | 0.6 | 10 |
| 63 | Incorporation of Europium into GaN Nanowires by Ion Implantation. Journal of Physical Chemistry C, 2019, 123, 11874-11887. | 1.5 | 12 |
| 64 | Engineering strain and conductivity of MoO3 by ion implantation. Acta Materialia, 2019, 169, 15-27. | 3.8 | 19 |
| 65 | Monte Carlo simulations of ion channeling in crystals containing dislocations and randomly displaced atoms. Journal of Applied Physics, 2019, 126, . | 1.1 | 21 |
| 66 | Optical and photoconductive properties of indium sulfide fluoride thin films. Thin Solid Films, 2019, 671, 49-52. | 0.8 | 5 |
| 67 | Influence of Al/Si atomic ratio on optical and electrical properties of magnetron sputtered Al1-xSixOy coatings. Thin Solid Films, 2019, 669, 475-481. | 0.8 | 4 |
| 68 | Analysis of deposited layers with deuterium and impurity elements on samples from the divertor of JET with ITER-like wall. Journal of Nuclear Materials, 2019, 516, 202-213. | 1.3 | 18 |
| 69 | Analysis of the outer divertor hot spot activity in the protection video camera recordings at JET. Fusion Engineering and Design, 2019, 139, 115-123. | 1.0 | 3 |
| 70 | Deposition temperature influence on the wear behaviour of carbon-based coatings deposited on hardened steel. Applied Surface Science, 2019, 475, 762-773. | 3.1 | 9 |
| 71 | Compositional analysis by RBS, XPS and EDX of ZnO:Al,Bi and ZnO:Ga,Bi thin films deposited by d.c. magnetron sputtering. Vacuum, 2019, 161, 268-275. | 1.6 | 26 |
| 72 | Improved neutron activation dosimetry for fusion. Fusion Engineering and Design, 2019, 139, 109-114. | 1.0 | 7 |

| # | Article | IF | Citations |
|---|---|---|---|
| 73 | RBS/C, XRR, and XRD Studies of Damage Buildup in Erâ€implanted ZnO. Physica Status Solidi (B): Basic Research, 2019, 256, 1800364. | 0.7 | 17 |
| 74 | CrAlSiN barrier layer to improve the thermal stability of W/CrAlSiNx/CrAlSiOyNx/SiAlOx solar thermal absorber. Solar Energy Materials and Solar Cells, 2019, 191, 235-242. | 3.0 | 17 |
| 75 | A study of solar thermal absorber stack based on CrAlSiNx/CrAlSiNxOy structure by ion beams. Nuclear Instruments & Methods in Physics Research B, 2019, 450, 195-199. | 0.6 | 5 |
| 76 | Measurement of proton induced Î³-ray emission cross sections on Na from 1.0 to 4.1 MeV. Nuclear Instruments & Methods in Physics Research B, 2019, 441, 108-118. | 0.6 | 8 |
| 77 | Defect formation and optical activation of Tb implanted AlxGa1â^'xN films using channeled implantation at different temperatures. Surface and Coatings Technology, 2018, 355, 29-39. | 2.2 | 9 |
| 78 | Helium load on W-O coatings grown by pulsed laser deposition. Surface and Coatings Technology, 2018, 355, 215-221. | 2.2 | 8 |
| 79 | WC-Cu thermal barriers for fusion applications. Surface and Coatings Technology, 2018, 355, 222-226. | 2.2 | 17 |
| 80 | Thin films of Agâ€“Au nanoparticles dispersed in TiO<sub>2</sub>: influence of composition and microstructure on the LSPR and SERS responses. Journal Physics D: Applied Physics, 2018, 51, 205102. | 1.3 | 30 |
| 81 | Up-conversion emission of aluminosilicate and titania films doped with Er3+/Yb3+ by ion implantation and sol-gel solution doping. Surface and Coatings Technology, 2018, 355, 162-168. | 2.2 | 14 |
| 82 | Backscattering analysis of short period ZnO/MgO superlattices. Surface and Coatings Technology, 2018, 355, 45-49. | 2.2 | 17 |
| 83 | Optical investigations of europium ion implanted in nitride-based diode structures. Surface and Coatings Technology, 2018, 355, 40-44. | 2.2 | 9 |
| 84 | Crystal damage analysis of implanted AlxGa1-xN (0â€¯â‰¤â€¯xâ€¯â‰¤â€¯1) by ion beam techniques. Surface and Coatings Technology, 2018, 355, 55-60. | 2.2 | 9 |
| 85 | Neutron spectroscopy measurements of 14 MeV neutrons at unprecedented energy resolution and implications for deuteriumâ€“tritium fusion plasma diagnostics. Measurement Science and Technology, 2018, 29, 045502. | 1.4 | 35 |
| 86 | A design of selective solar absorber for high temperature applications. Solar Energy, 2018, 172, 177-183. | 2.9 | 38 |
| 87 | Electrical characterization of molybdenum oxide lamellar crystals irradiated with UV light and proton beams. Surface and Coatings Technology, 2018, 355, 50-54. | 2.2 | 5 |
| 88 | Helium and deuterium irradiation effects in tungsten-based materials with titanium. Surface and Coatings Technology, 2018, 355, 143-147. | 2.2 | 1 |
| 89 | Radiation sensors based on GaN microwires. Journal Physics D: Applied Physics, 2018, 51, 175105. | 1.3 | 8 |
| 90 | Optimization of nanocomposite Au/TiO 2 thin films towards LSPR optical-sensing. Applied Surface Science, 2018, 438, 74-83. | 3.1 | 54 |

| # | Article | IF | Citations |
|---|---|---|---|
| 91 | Zr-O-N coatings for decorative purposes: Study of the system stability by exploration of the deposition parameter space. Surface and Coatings Technology, 2018, 343, 30-37. | 2.2 | 23 |
| 92 | In-situ XRD vs ex-situ vacuum annealing of tantalum oxynitride thin films: Assessments on the structural evolution. Applied Surface Science, 2018, 438, 14-19. | 3.1 | 1 |
| 93 | New WC-Cu thermal barriers for fusion applications: High temperature mechanical behaviour. Journal of Nuclear Materials, 2018, 498, 355-361. | 1.3 | 12 |
| 94 | Analysis of retained deuterium on Be-based films: Ion implantation vs. in-situ loading. Nuclear Materials and Energy, 2018, 17, 242-247. | 0.6 | 2 |
| 95 | Deuterium retention and erosion in liquid Sn samples exposed to D2 and Ar plasmas in GyM device. Nuclear Materials and Energy, 2018, 17, 253-258. | 0.6 | 17 |
| 96 | Multiple optical centers in Eu-implanted AlN nanowires for solid-state lighting applications. Applied Physics Letters, 2018, 113, 201905. | 1.5 | 8 |
| 97 | CuxCrFeMoTi (xâ€¯=â€¯0.21, 0.44, 1) high entropy alloys as novel materials for fusion applications. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2018, 238-239, 18-25. | 1.7 | 8 |
| 98 | Thin films composed of Au nanoparticles embedded in AlN: Influence of metal concentration and thermal annealing on the LSPR band. Vacuum, 2018, 157, 414-421. | 1.6 | 24 |
| 99 | Ion irradiation-induced easy-cone anisotropy in double-MgO free layers for perpendicular magnetic tunnel junctions. Applied Physics Letters, 2018, 112, . | 1.5 | 14 |
| 100 | In Situ Characterization and Modification of Î²â€Ga<sub>2</sub>O<sub>3</sub> Flakes Using an Ion Microâ€Probe. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800190. | 0.8 | 7 |
| 101 | Eu-Doped AlGaN/GaN Superlattice-Based Diode Structure for Red Lighting: Excitation Mechanisms and Active Sites. ACS Applied Nano Materials, 2018, 1, 3845-3858. | 2.4 | 14 |
| 102 | Thermal desorption spectrometry of beryllium plasma facing tiles exposed in the JET tokamak. Fusion Engineering and Design, 2018, 133, 135-141. | 1.0 | 19 |
| 103 | Assessment of erosion, deposition and fuel retention in the JET-ILW divertor from ion beam analysis data. Nuclear Materials and Energy, 2017, 12, 559-563. | 0.6 | 28 |
| 104 | Deuterium retention in tin (Sn) and lithiumâ€“tin (Liâ€“Sn) samples exposed to ISTTOK plasmas. Nuclear Materials and Energy, 2017, 12, 709-713. | 0.6 | 32 |
| 105 | Behavior of liquid Li-Sn alloy as plasma facing material on ISTTOK. Fusion Engineering and Design, 2017, 117, 208-211. | 1.0 | 18 |
| 106 | Asymmetric ZnO/ZnMgO double quantum well structures grown on m-plane ZnO substrates by MBE. Journal of Luminescence, 2017, 186, 262-267. | 1.5 | 10 |
| 107 | Studies of lithium deposition and D retention on tungsten samples exposed to Li-seeded plasmas in PISCES-A. Plasma Physics and Controlled Fusion, 2017, 59, 044006. | 0.9 | 4 |
| 108 | Efficient temperature sensing using photoluminescence of Er/Yb implanted GaN thin films. Sensors and Actuators B: Chemical, 2017, 248, 769-776. | 4.0 | 39 |

| # | Article | IF | Citations |
|---|---|---|---|
| 109 | Validity of Vegardâ€™s rule for Al1â^'xInxN (0.08â€‰â€‰<â€‰â€‰xâ€‰â€‰<â€‰â€‰0.28) thin films grown on GaN templates. Physics D: Applied Physics, 2017, 50, 205107. | 1.3 | 10 |
| 110 | Thermal and chemical stability of the Î²-W2N nitride phase. Nuclear Materials and Energy, 2017, 12, 462-467. | 0.6 | 20 |
| 111 | SiGe layer thickness effect on the structural and optical properties of well-organized SiGe/SiO2multilayers. Nanotechnology, 2017, 28, 345701. | 1.3 | 5 |
| 112 | Optical and structural analysis of solar selective absorbing coatings based on AlSiOx:W cermets. Solar Energy, 2017, 150, 335-344. | 2.9 | 40 |
| 113 | Helium and deuterium irradiation effects in W-Ta composites produced by pulse plasma compaction. Journal of Nuclear Materials, 2017, 492, 105-112. | 1.3 | 11 |
| 114 | Study of deuterium retention in Be-W coatings with distinct roughness profiles. Fusion Engineering and Design, 2017, 124, 464-467. | 1.0 | 7 |
| 115 | Overview of the JET ITER-like wall divertor. Nuclear Materials and Energy, 2017, 12, 499-505. | 0.6 | 46 |
| 116 | Effects of thermal annealing on the structural and electronic properties of rare earth-implanted MoO<sub>3</sub> nanoplates. CrystEngComm, 2017, 19, 2339-2348. | 1.3 | 6 |
| 117 | Fuel inventory and deposition in castellated structures in JET-ILW. Nuclear Fusion, 2017, 57, 066027. | 1.6 | 25 |
| 118 | Characterization of magnetron sputtered sub-stoichiometric CrAlSiN x and CrAlSiO y N x coatings. Surface and Coatings Technology, 2017, 328, 134-141. | 2.2 | 18 |
| 119 | Investigation and plasma cleaning of first mirrors coated with relevant ITER contaminants: beryllium and tungsten. Nuclear Fusion, 2017, 57, 086019. | 1.6 | 17 |
| 120 | Overview of the JET results in support to ITER. Nuclear Fusion, 2017, 57, 102001. | 1.6 | 150 |
| 121 | Overview of fuel inventory in JET with the ITER-like wall. Nuclear Fusion, 2017, 57, 086045. | 1.6 | 47 |
| 122 | Impurity re-distribution in the corner regions of the JET divertor. Physica Scripta, 2017, T170, 014060. | 1.2 | 6 |
| 123 | Experience on divertor fuel retention after two ITER-Like Wall campaigns. Physica Scripta, 2017, T170, 014063. | 1.2 | 26 |
| 124 | Doping Î²-Ga<sub>2</sub>O<sub>3</sub> with europium: influence of the implantation and annealing temperature. Journal Physics D: Applied Physics, 2017, 50, 325101. | 1.3 | 26 |
| 125 | Implantation damage formation in a-, c- and m-plane GaN. Acta Materialia, 2017, 123, 177-187. | 3.8 | 73 |
| 126 | Formation of metastable phases in Zr-ion-irradiated Al2O3 upon thermal annealing. Journal of Electron Microscopy, 2017, 66, 388-396. | 0.9 | 0 |

| # | Article | IF | Citations |
|---|---|---|---|
| 127 | Assessing material properties for fusion applications by ion beams. Nuclear Instruments & Methods in Physics Research B, 2017, 409, 255-258. | 0.6 | 2 |
| 128 | Time-resolved deposition in the remote region of the JET-ILW divertor: measurements and modelling. Physica Scripta, 2017, T170, 014059. | 1.2 | 6 |
| 129 | Plasmaâ€“wall interaction studies within the EUROfusion consortium: progress on plasma-facing components development and qualification. Nuclear Fusion, 2017, 57, 116041. | 1.6 | 75 |
| 130 | Corrosion Behavior of Titanium Oxynitrided by Diffusion and Magnetron Sputtering Methods in Physiological Solution. Materials Performance and Characterization, 2017, 6, 594-606. | 0.2 | 0 |
| 131 | Nanoscale triboactivity of functionalized c-Si surfaces by Fe<sup>+</sup>ion implantation. Journal of Physics Condensed Matter, 2016, 28, 134003. | 0.7 | 1 |
| 132 | Ag:TiNâ€€coated Polyurethane for Dry Biopotential Electrodes: From Polymer Plasma Interface Activation to the First EEG Measurements. Plasma Processes and Polymers, 2016, 13, 341-354. | 1.6 | 27 |
| 133 | Impact of implantation geometry and fluence on structural properties of AlxGa1-xN implanted with thulium. Journal of Applied Physics, 2016, 120, . | 1.1 | 10 |
| 134 | High Orbital Angular Momentum Harmonic Generation. Physical Review Letters, 2016, 117, 265001. | 2.9 | 66 |
| 135 | Utilization of native oxygen in Eu(RE)-doped GaN for enabling device compatibility in optoelectronic applications. Scientific Reports, 2016, 6, 18808. | 1.6 | 29 |
| 136 | Identifying the influence of the intrinsic defects in Gd-doped ZnO thin-films. Journal of Applied Physics, 2016, 119, . | 1.1 | 52 |
| 137 | Spectroscopic analysis of the NIR emission in Tm implanted AlxGa1-xN layers. Journal of Applied Physics, 2016, 120, 081701. | 1.1 | 9 |
| 138 | Correction to â€œSpectroscopic Analysis of Eu<sup>3+</sup> Implanted and Annealed GaN Layers and Nanowiresâ€• Journal of Physical Chemistry C, 2016, 120, 6907-6908. | 1.5 | 5 |
| 139 | Composition measurement of epitaxial Sc<sub>x</sub>Ga<sub>1â^'x</sub>N films. Semiconductor Science and Technology, 2016, 31, 064002. | 1.0 | 3 |
| 140 | Quantitative x-ray diffraction analysis of bimodal damage distributions in Tm implanted Al<sub>0.15</sub>Ga<sub>0.85</sub>N. Journal Physics D: Applied Physics, 2016, 49, 135308. | 1.3 | 19 |
| 141 | Electrical insulation properties of RF-sputtered LiPON layers towards electrochemical stability of lithium batteries. Journal Physics D: Applied Physics, 2016, 49, 485301. | 1.3 | 7 |
| 142 | Determination of 9Be(p,p0)9Be, 9Be(p,d0)8Be and 9Be(p,Î±0)6Li cross sections at 150Â° in the energy range 0.5â€“2.35 MeV. Nuclear Instruments & Methods in Physics Research B, 2016, 371, 50-53. | 0.6 | 9 |
| 143 | Anisotropy of electrical conductivity in dc due to intrinsic defect formation in Î±-Al2O3 single crystal implanted with Mg ions. Nuclear Instruments & Methods in Physics Research B, 2016, 379, 91-94. | 0.6 | 1 |
| 144 | Analysis of the Tb3+ recombination in ion implanted Al Ga1â^'N (0â‰¤xâ‰¤1) layers. Journal of Luminescence, 2016, 178, 249-258. | 1.5 | 7 |

| # | Article | IF | Citations |
|---|---|---|---|
| 145 | The role and application of ion beam analysis for studies of plasma-facing components in controlled fusion devices. Nuclear Instruments & Methods in Physics Research B, 2016, 371, 4-11. | 0.6 | 18 |
| 146 | Study of nuclear reactions producing<sup>36</sup>Cl by micro-AMS. Journal of Physics: Conference Series, 2016, 665, 012077. | 0.3 | 1 |
| 147 | Magnetoelectric effect probe through ppm Fe doping in BaTiO 3. Journal of Alloys and Compounds, 2016, 661, 495-500. | 2.8 | 6 |
| 148 | Functional behaviour of TiO<sub>2</sub> films doped with noble metals. Surface Engineering, 2016, 32, 554-561. | 1.1 | 14 |
| 149 | Deposition in the inner and outer corners of the JET divertor with carbon wall and metallic ITER-like wall. Physica Scripta, 2016, T167, 014052. | 1.2 | 14 |
| 150 | Study of damage formation and annealing of implanted III-nitride semiconductors for optoelectronic devices. Nuclear Instruments & Methods in Physics Research B, 2016, 379, 251-254. | 0.6 | 17 |
| 151 | Electrochemical characterization of nanostructured Ag:TiN thin films produced by glancing angle deposition on polyurethane substrates for bio-electrode applications. Journal of Electroanalytical Chemistry, 2016, 768, 110-120. | 1.9 | 12 |
| 152 | Long-term fuel retention in JET ITER-like wall. Physica Scripta, 2016, T167, 014075. | 1.2 | 52 |
| 153 | Mechanisms of Implantation Damage Formation in Al<sub>x</sub>Ga<sub>1â€“x</sub>N Compounds. Journal of Physical Chemistry C, 2016, 120, 7277-7283. | 1.5 | 33 |
| 154 | Quantum well intermixing and radiation effects in InGaN/GaN multi quantum wells. , 2016, , . | | 1 |
| 155 | Raman microscopy investigation of beryllium materials. Physica Scripta, 2016, T167, 014027. | 1.2 | 14 |
| 156 | Study of In distribution on GaInSb:Al crystals by ion beam techniques. Nuclear Instruments & Methods in Physics Research B, 2016, 371, 278-282. | 0.6 | 6 |
| 157 | Effect of AlN content on the lattice site location of terbium ions in Al<sub>x</sub>Ga<sub>1â^’x</sub>N compounds. Semiconductor Science and Technology, 2016, 31, 035026. | 1.0 | 12 |
| 158 | Quantitative Chemical Mapping of InGaN Quantum Wells from Calibrated High-Angle Annular Dark Field Micrographs. Microscopy and Microanalysis, 2015, 21, 994-1005. | 0.2 | 3 |
| 159 | Growth of mixed materials in the Be/W/O system in fusion devices. Microscopy and Microanalysis, 2015, 21, 94-95. | 0.2 | 0 |
| 160 | W-Ta Composites Consolidated by Spark Plasma Sintering. Microscopy and Microanalysis, 2015, 21, 27-28. | 0.2 | 0 |
| 161 | Luminescence studies on green emitting InGaN/GaN MQWs implanted with nitrogen. Scientific Reports, 2015, 5, 9703. | 1.6 | 19 |
| 162 | Photoluminescence studies of a perceived white light emission from a monolithic InGaN/GaN quantum well structure. Scientific Reports, 2015, 5, 13739. | 1.6 | 19 |

| # | Article | IF | Citations |
|---|---|---|---|
| 163 | Analysis of rotating collectors from the private region of JET with carbon wall and metallic ITER-like wall. Journal of Nuclear Materials, 2015, 463, 818-821. | 1.3 | 9 |
| 164 | Raman study of insulating and conductive ZnO:(Al, Mn) thin films. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2345-2354. | 0.8 | 16 |
| 165 | Analysis of the stability of InGaN/GaN multiquantum wells against ion beam intermixing. Nanotechnology, 2015, 26, 425703. | 1.3 | 6 |
| 166 | The effect of metalâ€rich growth conditions on the microstructure of Sc<sub>x</sub>Ga<sub>1â^'x</sub>N films grown using molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2837-2842. | 0.8 | 14 |
| 167 | Tribological characterization of TiO 2 /Au decorative thin films obtained by PVD magnetron sputtering technology. Wear, 2015, 330-331, 419-428. | 1.5 | 13 |
| 168 | Fuel retention in JET ITER-Like Wall from post-mortem analysis. Journal of Nuclear Materials, 2015, 463, 961-965. | 1.3 | 50 |
| 169 | Multifunctional Tiâ€“Me (Me=Al, Cu) thin film systems for biomedical sensing devices. Vacuum, 2015, 122, 353-359. | 1.6 | 20 |
| 170 | Structural characterization of dual ion implantation in silicon. Nuclear Instruments & Methods in Physics Research B, 2015, 365, 39-43. | 0.6 | 4 |
| 171 | Laser-induced diffusion decomposition in Feâ€“V thin-film alloys. Applied Surface Science, 2015, 336, 380-384. | 3.1 | 2 |
| 172 | Solar selective absorbers based on Al2O3:W cermets and AlSiN/AlSiON layers. Solar Energy Materials and Solar Cells, 2015, 137, 93-100. | 3.0 | 68 |
| 173 | Determination of the 9Be(3He,pi)11B (i=0,1,2,3) cross section at 135Â° in the energy range 1â€“2.5MeV. Nuclear Instruments & Methods in Physics Research B, 2015, 346, 21-25. | 0.6 | 24 |
| 174 | Electrochemical and structural characterization of nanocomposite Agy:TiNx thin films for dry bioelectrodes: the effect of the N/Ti ratio and Ag content. Electrochimica Acta, 2015, 153, 602-611. | 2.6 | 9 |
| 175 | Study of the electrical behavior of nanostructured Tiâ€“Ag thin films, prepared by Glancing Angle Deposition. Materials Letters, 2015, 157, 188-192. | 1.3 | 13 |
| 176 | Corundum-to-spinel structural phase transformation in alumina. Nuclear Instruments & Methods in Physics Research B, 2015, 358, 136-141. | 0.6 | 12 |
| 177 | Biological behaviour of thin films consisting of Au nanoparticles dispersed in a TiO2 dielectric matrix. Vacuum, 2015, 122, 360-368. | 1.6 | 20 |
| 178 | Spectroscopic Analysis of Eu<sup>3+</sup> Implanted and Annealed GaN Layers and Nanowires. Journal of Physical Chemistry C, 2015, 119, 17954-17964. | 1.5 | 13 |
| 179 | Ag y :TiN x thin films for dry biopotential electrodes: the effect of composition and structural changes on the electrical and mechanical behaviours. Applied Physics A: Materials Science and Processing, 2015, 119, 169-178. | 1.1 | 2 |
| 180 | Composition, structure and morphology of Al<sub>1â^'x</sub>In<sub>x</sub>N thin films grown on Al<sub>1â^'y</sub>Ga<sub>y</sub>N templates with different GaN contents. Journal Physics D: Applied Physics, 2015, 48, 015103. | 1.3 | 7 |

| # | Article | IF | Citations |
|---|---|---|---|
| 181 | Peculiar Magnetoelectric Coupling in BaTiO<sub>3</sub>:Fe<sub>113Âppm</sub> Nanoscopic Segregations. ACS Applied Materials & Interfaces, 2015, 7, 24741-24747. | 4.0 | 9 |
| 182 | Structure dependent resistivity and dielectric characteristics of tantalum oxynitride thin films produced by magnetron sputtering. Applied Surface Science, 2015, 354, 298-305. | 3.1 | 14 |
| 183 | Retention behaviour of deuterium and helium in beryllium under single D+ and dual He+/D+ exposure. Fusion Engineering and Design, 2015, 98-99, 1362-1366. | 1.0 | 4 |
| 184 | Composition and structure variation for magnetron sputtered tantalum oxynitride thin films, as function of deposition parameters. Applied Surface Science, 2015, 358, 508-517. | 3.1 | 7 |
| 185 | Global erosion and deposition patterns in JET with the ITER-like wall. Journal of Nuclear Materials, 2015, 463, 157-161. | 1.3 | 48 |
| 186 | Consolidation of Wâ€“Ta composites: Hot isostatic pressing and spark and pulse plasma sintering. Fusion Engineering and Design, 2015, 98-99, 1950-1955. | 1.0 | 31 |
| 187 | Optical properties of zirconium oxynitride films: The effect of composition, electronic and crystalline structures. Applied Surface Science, 2015, 358, 660-669. | 3.1 | 19 |
| 188 | Optical performance of thin films produced by the pulsed laser deposition of SiAlON and Er targets. Applied Surface Science, 2015, 336, 274-277. | 3.1 | 6 |
| 189 | Evolution of the functional properties of titaniumâ€“silver thin films for biomedical applications: Influence of in-vacuum annealing. Surface and Coatings Technology, 2015, 261, 262-271. | 2.2 | 19 |
| 190 | An overview of the comprehensive First Mirror Test in JET with ITER-like wall. Physica Scripta, 2014, T159, 014011. | 1.2 | 59 |
| 191 | High In-content InGaN layers synthesized by plasma-assisted molecular-beam epitaxy: Growth conditions, strain relaxation, and In incorporation kinetics. Journal of Applied Physics, 2014, 116, . | 1.1 | 36 |
| 192 | Intense luminescence emission from rare-earth-doped MoO3nanoplates and lamellar crystals for optoelectronic applications. Journal Physics D: Applied Physics, 2014, 47, 355105. | 1.3 | 28 |
| 193 | GaN:Pr<sup>3+</sup> nanostructures for red solid state light emission. RSC Advances, 2014, 4, 62869-62877. | 1.7 | 5 |
| 194 | Material migration patterns and overview of first surface analysis of the JET ITER-like wall. Physica Scripta, 2014, T159, 014010. | 1.2 | 75 |
| 195 | Doping of Ga<sub>2</sub>O<sub>3</sub>bulk crystals and NWs by ion implantation. Proceedings of SPIE, 2014, , . | 0.8 | 12 |
| 196 | First results and surface analysis strategy for plasma-facing components after JET operation with the ITER-like wall. Physica Scripta, 2014, T159, 014016. | 1.2 | 30 |
| 197 | Laser-assisted cleaning of beryllium-containing mirror samples from JET and PISCES-B. Fusion Engineering and Design, 2014, 89, 122-130. | 1.0 | 23 |
| 198 | Stopping power of 1H and 4He in lithium niobate. Nuclear Instruments & Methods in Physics Research B, 2014, 332, 330-333. | 0.6 | 3 |

| # | Article | IF | Citations |
|---|---|---|---|
| 199 | Study of the relationship between crystal structure and luminescence in rare-earth-implanted Ga2O3 nanowires during annealing treatments. Journal of Materials Science, 2014, 49, 1279-1285. | 1.7 | 29 |
| 200 | Measurement of proton induced Î³-ray emission cross sections on Al from 2.5 to 4.1MeV. Nuclear Instruments & Methods in Physics Research B, 2014, 332, 355-358. | 0.6 | 16 |
| 201 | Optimisation of surface treatments of TiO2:Nb transparent conductive coatings by a post-hot-wire annealing in a reducing H2 atmosphere. Thin Solid Films, 2014, 550, 404-412. | 0.8 | 20 |
| 202 | Electrochemical behaviour of nanocomposite Agx:TiN thin films for dry biopotential electrodes. Electrochimica Acta, 2014, 125, 48-57. | 2.6 | 30 |
| 203 | Ion beam induced epitaxial crystallization of Î±-Al2O3 at room temperature. Nuclear Instruments & Methods in Physics Research B, 2014, 321, 8-13. | 0.6 | 15 |
| 204 | Structural and optical properties of Ga auto-incorporated InAlN epilayers. Journal of Crystal Growth, 2014, 408, 97-101. | 0.7 | 19 |
| 205 | Europiumâ€doped GaN(Mg): beyond the limits of the lightâ€emitting diode. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 662-665. | 0.8 | 17 |
| 206 | Thermal Properties of Holmium-Implanted Gold Films. Journal of Low Temperature Physics, 2014, 176, 979-985. | 0.6 | 1 |
| 207 | Determination of Ga auto-incorporation in nominal InAlN epilayers grown by MOCVD. Journal of Materials Chemistry C, 2014, 2, 5787. | 2.7 | 21 |
| 208 | Surface analysis of tiles and samples exposed to the first JET campaigns with the ITER-like wall. Physica Scripta, 2014, T159, 014012. | 1.2 | 35 |
| 209 | Stopping power of C, O and Cl in tantalum oxide. Nuclear Instruments & Methods in Physics Research B, 2014, 332, 152-155. | 0.6 | 5 |
| 210 | Performance of resistive-charge position sensitive detectors for RBS/Channeling applications. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2014, 760, 98-106. | 0.7 | 5 |
| 211 | IBA study of SiGe/SiO2 nanostructured multilayers. Nuclear Instruments & Methods in Physics Research B, 2014, 331, 89-92. | 0.6 | 3 |
| 212 | Sequential multiple-step europium ion implantation and annealing of GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 253-257. | 0.8 | 9 |
| 213 | Composition and luminescence studies of InGaN epilayers grown at different hydrogen flow rates. Semiconductor Science and Technology, 2013, 28, 065011. | 1.0 | 13 |
| 214 | On the formation of an interface amorphous layer in nanostructured ferroelectric Ba0.8Sr0.2TiO3 thin films integrated on Ptâ€“Si and its effect on the electrical properties. Applied Surface Science, 2013, 278, 136-141. | 3.1 | 11 |
| 215 | Influence of RF-sputtering power on formation of vertically stacked Si<sub>1â^'x</sub>Ge<sub>x</sub>nanocrystals between ultra-thin amorphous Al<sub>2</sub>O<sub>3</sub>layers: structural and photoluminescence properties. Journal Physics D: Applied Physics, 2013, 46, 385301. | 1.3 | 1 |
| 216 | TiAgx thin films for lower limb prosthesis pressure sensors: Effect of composition and structural changes on the electrical and thermal response of the films. Applied Surface Science, 2013, 285, 10-18. | 3.1 | 34 |

| # | Article | IF | Citations |
|---|---|---|---|
| 217 | Nanocomposite Ag:TiN thin films for dry biopotential electrodes. Applied Surface Science, 2013, 285, 40-48. | 3.1 | 38 |
| 218 | Status of the MARE Experiment. IEEE Transactions on Applied Superconductivity, 2013, 23, 2101204-2101204. | 1.1 | 3 |
| 219 | Influence of stoichiometry and structure on the optical properties of AlN<sub>x</sub>O<sub>y</sub> films. Journal Physics D: Applied Physics, 2013, 46, 015305. | 1.3 | 24 |
| 220 | Microstructure and nanomechanical properties of Fe+ implanted silicon. Applied Surface Science, 2013, 284, 533-539. | 3.1 | 7 |
| 221 | Structural and luminescence properties of Eu and Er implanted Bi2O3 nanowires for optoelectronic applications. Journal of Materials Chemistry C, 2013, 1, 7920. | 2.7 | 38 |
| 222 | p-Type <formula formulatype="inline"><tex Notation="TeX">${hbox{Cu}}_{x}{hbox{O}}$</tex> </formula> Thin-Film Transistors Produced by Thermal Oxidation. Journal of Display Technology, 2013, 9, 735-740. | 1.3 | 34 |
| 223 | CdTe nano-structures for photovoltaic devices. Nuclear Instruments & Methods in Physics Research B, 2013, 306, 218-221. | 0.6 | 2 |
| 224 | The influence of photon excitation and proton irradiation on the luminescence properties of yttria stabilized zirconia doped with praseodymium ions. Nuclear Instruments & Methods in Physics Research B, 2013, 306, 207-211. | 0.6 | 2 |
| 225 | Enhanced red emission from praseodymium-doped GaN nanowires by defect engineering. Acta Materialia, 2013, 61, 3278-3284. | 3.8 | 22 |
| 226 | Editorial â€“ 13th ICNMTA 2012. Nuclear Instruments & Methods in Physics Research B, 2013, 306, 1-2. | 0.6 | 0 |
| 227 | Formation of oriented nickel aggregates in rutile single crystals by Ni implantation. Journal of Magnetism and Magnetic Materials, 2013, 340, 102-108. | 1.0 | 7 |
| 228 | Properties of tantalum oxynitride thin films produced by magnetron sputtering: The influence of processing parameters. Vacuum, 2013, 98, 63-69. | 1.6 | 33 |
| 229 | Lattice site location and luminescence studies of AlxGa1â^'xN alloys doped with thulium ions. Nuclear Instruments & Methods in Physics Research B, 2013, 307, 495-498. | 0.6 | 6 |
| 230 | Blistering of Wâ€“Ta composites at different irradiation energies. Journal of Nuclear Materials, 2013, 438, S1032-S1035. | 1.3 | 20 |
| 231 | Effects of helium and deuterium irradiation on SPS sintered Wâ€“Ta composites at different temperatures. Journal of Nuclear Materials, 2013, 442, S251-S255. | 1.3 | 17 |
| 232 | Measurement and evaluation of the 13C(p,p)13C cross section in the energy range 0.8â€“2.4MeV. Nuclear Instruments & Methods in Physics Research B, 2013, 316, 81-87. | 0.6 | 5 |
| 233 | Synergistic helium and deuterium blistering in tungstenâ€“tantalum composites. Journal of Nuclear Materials, 2013, 442, 69-74. | 1.3 | 21 |
| 234 | Development of tantalum oxynitride thin films produced by PVD: Study of structural stability. Applied Surface Science, 2013, 285, 19-26. | 3.1 | 13 |

| # | Article | IF | Citations |
|---|---|---|---|
| 235 | Formation and delamination of beryllium carbide films. Journal of Nuclear Materials, 2013, 442, S320-S324. | 1.3 | 11 |
| 236 | A comparative study of photo-, cathodo- and ionoluminescence of GaN nanowires implanted with rare earth ions. Nuclear Instruments & Methods in Physics Research B, 2013, 306, 201-206. | 0.6 | 8 |
| 237 | Local deposition of 13C tracer in the JET MKII-HD divertor. Journal of Nuclear Materials, 2013, 438, S762-S765. | 1.3 | 1 |
| 238 | Saturation of hydrogen retention in gallium samples exposed to tokamak ISTTOK plasmas. Journal of Nuclear Materials, 2013, 438, S992-S995. | 1.3 | 2 |
| 239 | Nanostructures and thin films of transparent conductive oxides studied by perturbed angular correlations. Physica Status Solidi (B): Basic Research, 2013, 250, 801-808. | 0.7 | 4 |
| 240 | Microprobe analysis, iono- and photo-luminescence of Mn2+ activated ZnGa2O4 fibres. Nuclear Instruments & Methods in Physics Research B, 2013, 306, 195-200. | 0.6 | 12 |
| 241 | Extended-Gate ISFETs Based on Sputtered Amorphous Oxides. Journal of Display Technology, 2013, 9, 729-734. | 1.3 | 16 |
| 242 | Towards the understanding of the intentionally induced yellow luminescence in GaN nanowires. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 667-672. | 0.8 | 8 |
| 243 | Influence of composition, bonding characteristics and microstructure on the electrochemical and optical stability of AlOxNy thin films. Electrochimica Acta, 2013, 106, 23-34. | 2.6 | 11 |
| 244 | Comparison of low- and room-temperature damage formation in Ar ion implanted GaN and ZnO. Nuclear Instruments & Methods in Physics Research B, 2013, 307, 394-398. | 0.6 | 34 |
| 245 | Temperature-dependent hysteresis of the emission spectrum of Eu-implanted, Mg-doped HVPE GaN. AIP Conference Proceedings, 2013, , . | 0.3 | 5 |
| 246 | Thermal properties of holmium-implanted gold films for a neutrino mass experiment with cryogenic microcalorimeters. Review of Scientific Instruments, 2013, 84, 083905. | 0.6 | 6 |
| 247 | On the origin of strain relaxation in epitaxial CdZnO layers. , 2013, , . | | 0 |
| 248 | Spectroscopy of radiation defects in rutile TiO<sub>2</sub>. Physica Status Solidi (B): Basic Research, 2013, 250, 843-849. | 0.7 | 2 |
| 249 | The defect structure of sapphire produced by implantation of Zr and Zr plus O: threshold fluence for amorphization and optical properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 202-207. | 0.8 | 2 |
| 250 | Disorder induced violet/blue luminescence in rfâ€deposited ZnO films. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 662-666. | 0.8 | 13 |
| 251 | Investigation of generation of defects due to metallization on CdZnTe detectors. Journal Physics D: Applied Physics, 2012, 45, 175102. | 1.3 | 14 |
| 252 | Structural and Electrical Properties of Nanostructured Ba<sub>0.8</sub>Sr<sub>0.2</sub>TiO<sub>3</sub> Films Deposited by Pulsed Laser Deposition. Journal of Nano Research, 2012, 18-19, 299-306. | 0.8 | 0 |

| # | Article | IF | Citations |
|---|---|---|---|
| 253 | TiO<sub>2</sub> coatings with Au nanoparticles analysed by photothermal IR radiometry. Journal Physics D: Applied Physics, 2012, 45, 105301. | 1.3 | 17 |
| 254 | Tuning the properties of Ge-quantum dots superlattices in amorphous silica matrix through deposition conditions. Journal of Applied Physics, 2012, 111, 074316. | 1.1 | 4 |
| 255 | Ion beams as a tool for the characterization of near-pseudomorphic CdZnO epilayers. , 2012, , . | | 1 |
| 256 | Enhanced dynamic annealing and optical activation of Eu implanted a-plane GaN. Europhysics Letters, 2012, 97, 68004. | 0.7 | 15 |
| 257 | Structural and magnetic properties of thin films of BaFeO3-Î´ deposited by pulsed injection metal-organic chemical vapor deposition. Journal of Applied Physics, 2012, 111, . | 1.1 | 9 |
| 258 | Electroless deposition of Au, Pt, or Ru metallic layers on CdZnTe. Thin Solid Films, 2012, 525, 56-63. | 0.8 | 16 |
| 259 | Carbon Deposition on Beryllium Substrates and Subsequent Delamination. Materials Science Forum, 2012, 730-732, 179-184. | 0.3 | 0 |
| 260 | Influence of annealing conditions on the formation of regular lattices of voids and Ge quantum dots in an amorphous alumina matrix. Nanotechnology, 2012, 23, 405605. | 1.3 | 8 |
| 261 | Single phase a-plane MgZnO epilayers for UV optoelectronics: substitutional behaviour of Mg at large contents. CrystEngComm, 2012, 14, 1637-1640. | 1.3 | 29 |
| 262 | Electrical properties of AlNxOy thin films prepared by reactive magnetron sputtering. Thin Solid Films, 2012, 520, 6709-6717. | 0.8 | 24 |
| 263 | Optical properties of LFZ grown Î²-Ga2O3:Eu3+ fibres. Applied Surface Science, 2012, 258, 9157-9161. | 3.1 | 28 |
| 264 | The influence of annealing treatments on the properties of Ag:TiO2 nanocomposite films prepared by magnetron sputtering. Applied Surface Science, 2012, 258, 4028-4034. | 3.1 | 49 |
| 265 | Deposition of nanometric double layers Ru/Au, Ru/Pd, and Pd/Au onto CdZnTe by the electroless method. Journal of Crystal Growth, 2012, 358, 89-93. | 0.7 | 9 |
| 266 | TiNx coated polycarbonate for bio-electrode applications. Corrosion Science, 2012, 56, 49-57. | 3.0 | 37 |
| 267 | Doped gallium oxide nanowires for photonics. Proceedings of SPIE, 2012, , . | 0.8 | 10 |
| 268 | Characterization of TiAlSiN/TiAlSiON/SiO2 optical stack designed by modelling calculations for solar selective applications. Solar Energy Materials and Solar Cells, 2012, 105, 202-207. | 3.0 | 70 |
| 269 | Damage formation and recovery in Fe implanted 6Hâ€“SiC. Nuclear Instruments & Methods in Physics Research B, 2012, 286, 89-92. | 0.6 | 4 |
| 270 | Surface morphology, thermal and electrical conductivity of Î±-Al2O3 single crystals implanted with Au and Ag ions. Nuclear Instruments & Methods in Physics Research B, 2012, 286, 184-189. | 0.6 | 4 |

| # | Article | IF | Citations |
|---|---|---|---|
| 271 | Cd ion implantation in AlN. Nuclear Instruments & Methods in Physics Research B, 2012, 289, 43-46. | 0.6 | 6 |
| 272 | High pressure annealing of Europium implanted GaN. Proceedings of SPIE, 2012, , . | 0.8 | 23 |
| 273 | Structural and electrical studies of ultrathin layers with Si0.7Ge0.3 nanocrystals confined in a SiGe/SiO2 superlattice. Journal of Applied Physics, 2012, 111, 104323. | 1.1 | 10 |
| 274 | Electronic structure of ytterbium-implanted GaN at ambient and high pressure: experimental and crystal field studies. Journal of Physics Condensed Matter, 2012, 24, 095803. | 0.7 | 1 |
| 275 | The electronic transport mechanism in indium molybdenum oxide thin films RF sputtered at room temperature. Europhysics Letters, 2012, 97, 36002. | 0.7 | 9 |
| 276 | Optical doping of Al[sub x]Ga[sub 1â^'x]N compounds by ion implantation of Tm ions. AIP Conference Proceedings, 2012, , . | 0.3 | 5 |
| 277 | Unintentional incorporation of H and related structural and freeâ€electron properties of câ€and aâ€plane InN. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 91-94. | 0.8 | 4 |
| 278 | Ion implantation of Cd and Ag into AlN and GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1060-1064. | 0.8 | 9 |
| 279 | Rare earth co-doping nitride layers for visible light. Materials Chemistry and Physics, 2012, 134, 716-720. | 2.0 | 16 |
| 280 | Structural and optical studies of Au doped titanium oxide films. Nuclear Instruments & Methods in Physics Research B, 2012, 272, 61-65. | 0.6 | 16 |
| 281 | Stopping power of He, C and O in TiO2. Nuclear Instruments & Methods in Physics Research B, 2012, 273, 22-25. | 0.6 | 8 |
| 282 | Stopping power of He, C and O in GaN. Nuclear Instruments & Methods in Physics Research B, 2012, 273, 26-29. | 0.6 | 3 |
| 283 | Stopping power of C in Si. Nuclear Instruments & Methods in Physics Research B, 2012, 273, 30-32. | 0.6 | 5 |
| 284 | High precision determination of the InN content of Al1â^'xInxN thin films by Rutherford backscattering spectrometry. Nuclear Instruments & Methods in Physics Research B, 2012, 273, 105-108. | 0.6 | 8 |
| 285 | Incorporation of N in TiO2 films grown by DC-reactive magnetron sputtering. Nuclear Instruments & Methods in Physics Research B, 2012, 273, 109-112. | 0.6 | 13 |
| 286 | AlN content influence on the properties of AlxGa1â^'xN doped with Pr ions. Nuclear Instruments & Methods in Physics Research B, 2012, 273, 149-152. | 0.6 | 4 |
| 287 | Characterization of nanostructured HfO2 films using RBS and PAC. Nuclear Instruments & Methods in Physics Research B, 2012, 273, 195-198. | 0.6 | 1 |
| 288 | Analysis of multifunctional titanium oxycarbide films as a function of oxygen addition. Surface and Coatings Technology, 2012, 206, 2525-2534. | 2.2 | 27 |

| # | Article | IF | Citations |
|---|---|---|---|
| 289 | Tuning of the surface plasmon resonance in TiO2/Au thin films grown by magnetron sputtering: The effect of thermal annealing. Journal of Applied Physics, 2011, 109, . | 1.1 | 74 |
| 290 | Electroless plating of Au, Pt, or Ru thin film layer on CdZnTe. , 2011, , . | | 1 |
| 291 | Cathodoluminescence of rare earth implanted Ga2O3and GeO2nanostructures. Nanotechnology, 2011, 22, 285706. | 1.3 | 39 |
| 292 | Radiation damage formation and annealing in GaN and ZnO. Proceedings of SPIE, 2011, , . | 0.8 | 54 |
| 293 | Resonant Raman scattering in ZnO:Mn and ZnO:Mn:Al thin films grown by RF sputtering. Journal of Physics Condensed Matter, 2011, 23, 334205. | 0.7 | 26 |
| 294 | Comparative study of fusion relevant properties of Be12V and Be12Ti. Fusion Engineering and Design, 2011, 86, 2454-2457. | 1.0 | 9 |
| 295 | Microstructural characterization of the ODS Eurofer 97 EU-batch. Fusion Engineering and Design, 2011, 86, 2386-2389. | 1.0 | 12 |
| 296 | Tritium permeation, retention and release properties of beryllium pebbles. Fusion Engineering and Design, 2011, 86, 2338-2342. | 1.0 | 9 |
| 297 | Hydrogen retention in gallium samples exposed to ISTTOK plasmas. Fusion Engineering and Design, 2011, 86, 2458-2461. | 1.0 | 4 |
| 298 | Surface composition and morphology changes of JET tiles under plasma interactions. Fusion Engineering and Design, 2011, 86, 2557-2560. | 1.0 | 6 |
| 299 | Deposition of13C tracer in the JET MkII-HD divertor. Physica Scripta, 2011, T145, 014004. | 1.2 | 15 |
| 300 | Optical properties of AlN x O y thin films deposited by DC magnetron sputtering. , 2011, , . | | 3 |
| 301 | Mass spectrometry improvement on an high current ion implanter. Nuclear Instruments & Methods in Physics Research B, 2011, 269, 3222-3225. | 0.6 | 0 |
| 302 | Materials research under ITER-like divertor conditions at FOM Rijnhuizen. Journal of Nuclear Materials, 2011, 417, 457-462. | 1.3 | 1 |
| 303 | Tungstenâ€“microdiamond composites for plasma facing components. Journal of Nuclear Materials, 2011, 416, 45-48. | 1.3 | 6 |
| 304 | Effect of Eu-implantation and annealing on the GaN quantum dots excitonic recombination. Nanoscale Research Letters, 2011, 6, 378. | 3.1 | 6 |
| 305 | Colossal dielectric constant of poly- and single-crystalline CaCu3Ti4O12 fibres grown by the laser floating zone technique. Acta Materialia, 2011, 59, 102-111. | 3.8 | 27 |
| 306 | Low-temperature fabrication of layered self-organized Ge clusters by RF-sputtering. Nanoscale Research Letters, 2011, 6, 341. | 3.1 | 18 |

| # | Article | IF | Citations |
|---|---|---|---|
| 307 | Free electron properties and hydrogen in InN grown by MOVPE. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1179-1182. | 0.8 | 9 |
| 308 | Comparison of radiation detector performance for different metal contacts on CdZnTe deposited by electroless deposition method. Crystal Research and Technology, 2011, 46, 1131-1136. | 0.6 | 24 |
| 309 | Ageing effects on the wettability behavior of laser textured silicon. Applied Surface Science, 2011, 257, 2604-2609. | 3.1 | 16 |
| 310 | Preparation and characterization of CrNxOy thin films: The effect of composition and structural features on the electrical behavior. Applied Surface Science, 2011, 257, 9120-9124. | 3.1 | 19 |
| 311 | The photoluminescence/excitation (PL/E) spectroscopy of Eu-implanted GaN. Optical Materials, 2011, 33, 1063-1065. | 1.7 | 27 |
| 312 | Rapid thermal annealing of rare earth implanted ZnO epitaxial layers. Optical Materials, 2011, 33, 1139-1142. | 1.7 | 33 |
| 313 | The role of the annealing temperature on the optical and structural properties of Eu doped GaN/AlN QD. Optical Materials, 2011, 33, 1045-1049. | 1.7 | 3 |
| 314 | Influence of the deposition parameters on the growth of SiGe nanocrystals embedded in Al2O3 matrix. Microelectronic Engineering, 2011, 88, 509-513. | 1.1 | 8 |
| 315 | Structural and optical properties of Er implanted AlN thin films: Green and infrared photoluminescence at room temperature. Optical Materials, 2011, 33, 1055-1058. | 1.7 | 11 |
| 316 | Mechanisms of damage formation in Eu-implanted GaN probed by X-ray diffraction. Europhysics Letters, 2011, 96, 46002. | 0.7 | 39 |
| 317 | The high sensitivity of InN under rare earth ion implantation at medium range energy. Journal Physics D: Applied Physics, 2011, 44, 295402. | 1.3 | 13 |
| 318 | Optimization Of A Mass Spectrometry Process. , 2011, , . | | 0 |
| 319 | A Double Scattering Analytical Model For Elastic Recoil Detection Analysis. , 2011, , . | | 1 |
| 320 | Unintentional incorporation of hydrogen in wurtzite InN with different surface orientations. Journal of Applied Physics, 2011, 110, . | 1.1 | 3 |
| 321 | Zeeman splittings of the <sup>5</sup>D<sub>0</sub>â€“<sup>7</sup>F<sub>2</sub> transitions of Eu<sup>3+</sup> ions implanted into GaN. Materials Research Society Symposia Proceedings, 2011, 1290, 1. | 0.1 | 6 |
| 322 | Damage formation in GaN under medium energy range implantation of rare earth ions: a combined TEM, XRD and RBS/C investigation. Materials Research Society Symposia Proceedings, 2011, 1342, 35. | 0.1 | 0 |
| 323 | Ternary AlGaN Alloys with High Al Content and Enhanced Compositional Homogeneity Grown by Plasma-Assisted Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 031001. | 0.8 | 9 |
| 324 | Integration Of SIMS Into A General Purpose IBA Data Analysis Code. AIP Conference Proceedings, 2011, , . | 0.3 | 4 |

| # | Article | IF | Citations |
|---|---|---|---|
| 325 | Hydrogen In Group-III Nitrides: An Ion Beam Analysis Study. , 2011, , . | | 1 |
| 326 | Stopping Power Of He, C And O In InN. , 2011, , . | | 2 |
| 327 | N-Doped Photocatalytic Titania Thin Films on Active Polymer Substrates. Journal of Nanoscience and Nanotechnology, 2010, 10, 1072-1077. | 0.9 | 11 |
| 328 | Crystal Size and Crystalline Volume Fraction Effects on the Erbium Emission of nc-Si:Er Grown by r.f. Sputtering. Journal of Nanoscience and Nanotechnology, 2010, 10, 2663-2668. | 0.9 | 5 |
| 329 | Influence of Deposition Pressure on N-doped ZnO Films by RF Magnetron Sputtering. Journal of Nanoscience and Nanotechnology, 2010, 10, 2674-2678. | 0.9 | 3 |
| 330 | Defect studies and optical activation of Yb doped GaN. Journal of Physics: Conference Series, 2010, 249, 012053. | 0.3 | 2 |
| 331 | Effect of grain size and hydrogen passivation on the electrical properties of nanocrystalline silicon films. International Journal of Materials and Product Technology, 2010, 39, 195. | 0.1 | 5 |
| 332 | Influence of temperature and plasma composition on deuterium retention in refractory metals. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 2124-2128. | 0.6 | 2 |
| 333 | Effect of Eu2O3 doping on Ta2O5 crystal growth by the laser-heated pedestal technique. Journal of Crystal Growth, 2010, 313, 62-67. | 0.7 | 7 |
| 334 | Single and polycrystalline mullite fibres grown by laser floating zone technique. Journal of the European Ceramic Society, 2010, 30, 3311-3318. | 2.8 | 20 |
| 335 | Multilayers of Ge nanocrystals embedded in Al2O3 matrix: Structural and electrical studies. Microelectronic Engineering, 2010, 87, 2508-2512. | 1.1 | 8 |
| 336 | Carbon film growth and hydrogenic retention of tungsten exposed to carbon-seeded high density deuterium plasmas. Journal of Nuclear Materials, 2010, 396, 176-180. | 1.3 | 2 |
| 337 | Stopping power of 11B in Si and TiO2 measured with a bulk sample method and Bayesian inference data analysis. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 1768-1771. | 0.6 | 10 |
| 338 | High Resolution and Differential PIXE combined with RBS, EBS and AFM analysis of magnesium titanate (MgTiO3) multilayer structures. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 1980-1985. | 0.6 | 20 |
| 339 | Erosion and re-deposition processes in JET tiles studied with ion beams. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 1991-1996. | 0.6 | 15 |
| 340 | Effects of Mg-ion implantation in Î±-Al2O3 and Î±-Al2O3:Mg crystals: Electrical conductivity and electronic structure changes. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 2874-2877. | 0.6 | 3 |
| 341 | High temperature annealing of Europium implanted AlN. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 2907-2910. | 0.6 | 4 |
| 342 | Damage recovery and optical activity in europium implanted wide gap oxides. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 3137-3141. | 0.6 | 5 |

| # | Article | IF | Citations |
|---|---|---|---|
| 343 | Structural study of Si1â^'xGex nanocrystals embedded in SiO2 films. Thin Solid Films, 2010, 518, 2569-2572. | 0.8 | 9 |
| 344 | Strain dependence electrical resistance and cohesive strength of ITO thin films deposited on electroactive polymer. Thin Solid Films, 2010, 518, 4525-4528. | 0.8 | 13 |
| 345 | Room temperature paramagnetism of ZnO:Mn films grown by RF-sputtering. Thin Solid Films, 2010, 518, 4612-4614. | 0.8 | 7 |
| 346 | Functional and optical properties of Au:TiO2 nanocomposite films: The influence of thermal annealing. Applied Surface Science, 2010, 256, 6536-6542. | 3.1 | 43 |
| 347 | Al1â^'xInxN/GaN bilayers: Structure, morphology, and optical properties. Physica Status Solidi (B): Basic Research, 2010, 247, 1740-1746. | 0.7 | 10 |
| 348 | Influence of thermal annealing on the structural and optical properties of GaN/AlN quantum dots. Physica Status Solidi (B): Basic Research, 2010, 247, 1675-1678. | 0.7 | 5 |
| 349 | Total reflectance and Raman studies in Al<sub>y</sub>In<sub>x</sub>Ga<sub>1â€xâ€y</sub>N epitaxial layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 56-59. | 0.8 | 0 |
| 350 | Erbium-doped nanocrystalline silicon thin films produced by RF sputtering - annealing effect on the Er emission. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, NA-NA. | 0.8 | 2 |
| 351 | Raman study of dopedâ€ZnO thin films grown by rf sputtering. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2290-2293. | 0.8 | 13 |
| 352 | Growth and characterization of Mnâ€doped ZnO/TiO<sub>2</sub> multilayer nanostructures grown by pulsed laser deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2724-2726. | 0.8 | 0 |
| 353 | Effect of annealing on AlN/GaN quantum dot heterostructures: advanced ion beam characterization and Xâ€ray study of lowâ€dimensional structures. Surface and Interface Analysis, 2010, 42, 1552-1555. | 0.8 | 6 |
| 354 | The Characterization of N Interstitials and Dangling Bond Point Defects on Ionâ€Implanted GaN Nanowires Studied by Photoluminescence and Xâ€Ray Absorption Spectroscopy. Journal of the American Ceramic Society, 2010, 93, 3531-3534. | 1.9 | 7 |
| 355 | Electrical and Raman Scattering Studies of ZnO:P and ZnO:Sb Thin Films. Journal of Nanoscience and Nanotechnology, 2010, 10, 2620-2623. | 0.9 | 8 |
| 356 | Consolidation of Cu-nDiamond Nanocomposites: Hot Extrusion vs Spark Plasma Sintering. Materials Science Forum, 2010, 636-637, 682-687. | 0.3 | 14 |
| 357 | Hydrogenic retention of high-Z refractory metals exposed to ITER divertor-relevant plasma conditions. Nuclear Fusion, 2010, 50, 055004. | 1.6 | 17 |
| 358 | High Mobility a-IGO Films Produced at Room Temperature and Their Application in TFTs. Electrochemical and Solid-State Letters, 2010, 13, H20. | 2.2 | 52 |
| 359 | Defects in Irradiated ZnO Thin Films Studied by Photoluminescence and Photoconductivity. Materials Research Society Symposia Proceedings, 2010, 1268, 1. | 0.1 | 1 |
| 360 | Functionalizing self-assembled GaN quantum dot superlattices by Eu-implantation. Journal of Applied Physics, 2010, 108, 084306. | 1.1 | 16 |

| # | Article | IF | Citations |
|---|---|---|---|
| 361 | Hydrogen in InN: A ubiquitous phenomenon in molecular beam epitaxy grown material. Applied Physics Letters, 2010, 96, . | 1.5 | 36 |
| 362 | Lattice site location of optical centers in GaN:Eu light emitting diode material grown by organometallic vapor phase epitaxy. Applied Physics Letters, 2010, 97, 111911. | 1.5 | 29 |
| 363 | Optical doping and damage formation in AlN by Eu implantation. Journal of Applied Physics, 2010, 107, 023525. | 1.1 | 38 |
| 364 | Structural anisotropy of nonpolar and semipolar InN epitaxial layers. Journal of Applied Physics, 2010, 108, . | 1.1 | 21 |
| 365 | Indium kinetics during the plasma-assisted molecular beam epitaxy of semipolar (11â^22) InGaN layers. Applied Physics Letters, 2010, 96, 181907. | 1.5 | 27 |
| 366 | Isotopic fingerprints of Pt-containing luminescence centers in highly enrichedS28i. Physical Review B, 2010, 81, . | 1.1 | 10 |
| 367 | Mn-doped ZnO nanocrystals embedded in Al<sub>2</sub>O<sub>3</sub>: structural and electrical properties. Nanotechnology, 2010, 21, 505705. | 1.3 | 11 |
| 368 | Optical and Structural Properties of an Eu Implanted Gallium Nitride Quantum Dots/Aluminium Nitride Superlattice. Journal of Nanoscience and Nanotechnology, 2010, 10, 2473-2478. | 0.9 | 3 |
| 369 | Depth-resolved analysis of spontaneous phase separation in the growth of lattice-matched AlInN. Journal Physics D: Applied Physics, 2010, 43, 055406. | 1.3 | 33 |
| 370 | Improved Route for the Synthesis of Colloidal NaYF<SUB>4</SUB> Nanocrystals and Electron Spin Resonance of Gd<SUP>3+</SUP> Local Probe. Journal of Nanoscience and Nanotechnology, 2010, 10, 5708-5714. | 0.9 | 1 |
| 371 | Structural and thermal characterization of SiO2â€“P2O5 solâ€“gel powders upon annealing at high temperatures. Journal of Non-Crystalline Solids, 2010, 356, 495-501. | 1.5 | 21 |
| 372 | Identification of the prime optical center in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>GaN</mml:mtext><mml:mo>:</mml:mo><mml:msup><mml:mrow><mml:mtext>Eu</mml:mtext></mml:mrow></mml:msup></mml:mrow></mml:math>. Physical Review B, 2010, 81, . | 1.1 | 90 |
| 373 | RE Implantation and Annealing of III-Nitrides. Topics in Applied Physics, 2010, , 25-54. | 0.4 | 7 |
| 374 | Computer Control of a 3 MV Van de Graaff Accelerator. Metrology and Measurement Systems, 2010, 17, 415-425. | 1.4 | 0 |
| 375 | The Structure of Sapphire Implanted with Carbon at Room Temperature and 1000Â°â€‰C. , 2009, , . | | 1 |
| 376 | Stopping Power of Different Ions in Si Measured with a Bulk Sample Method and Bayesian Inference Data Analysis. , 2009, , . | | 9 |
| 377 | Luminescence of Eu ions in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub></mml:mrow></mml:math> the entire alloy composition range. Physical Review B, 2009, 80, . | 1.1 | 31 |
| 378 | Enhancement in the photocatalytic nature of nitrogen-doped PVD-grown titanium dioxide thin films. Journal of Applied Physics, 2009, 106, . | 1.1 | 37 |

| # | Article | IF | Citations |
|---|---|---|---|
| 379 | Structural and optical properties of Zn0.9Mn0.1O/ZnO core-shell nanowires designed by pulsed laser deposition. Journal of Applied Physics, 2009, 106, . | 1.1 | 13 |
| 380 | Optical and structural properties of Eu-implanted InxAl1â˜'xN. Journal of Applied Physics, 2009, 106, . | 1.1 | 3 |
| 381 | Room-Temperature Cosputtered HfO[sub 2]â€“Al[sub 2]O[sub 3] Multicomponent Gate Dielectrics. Electrochemical and Solid-State Letters, 2009, 12, G65. | 2.2 | 22 |
| 382 | Structural and optical characterization of Eu-implanted GaN. Journal Physics D: Applied Physics, 2009, 42, 165103. | 1.3 | 48 |
| 383 | Nanoscale Materials Defect Characterisation. Particle Acceleration and Detection, 2009, , 185-204. | 0.3 | 0 |
| 384 | Optically active centers in Eu implanted, Euin situdoped GaN, and Eu doped GaN quantum dots. Journal of Applied Physics, 2009, 105, 043104. | 1.1 | 38 |
| 385 | Breakdown of anomalous channeling with ion energy for accurate strain determination in GaN-based heterostructures. Applied Physics Letters, 2009, 95, 051921. | 1.5 | 5 |
| 386 | Influence of steering effects on strain detection in AlGaInN/GaN heterostructures by ion channelling. Journal Physics D: Applied Physics, 2009, 42, 065420. | 1.3 | 6 |
| 387 | Intrinsic <I>p</I> Type ZnO Films Deposited by rf Magnetron Sputtering. Journal of Nanoscience and Nanotechnology, 2009, 9, 813-816. | 0.9 | 7 |
| 388 | Europium doping of zincblende GaN by ion implantation. Journal of Applied Physics, 2009, 105, 113507. | 1.1 | 8 |
| 389 | Hydrogenic retention in tungsten exposed to ITER divertor relevant plasma flux densities. Journal of Nuclear Materials, 2009, 390-391, 610-613. | 1.3 | 14 |
| 390 | Characterisation of titanium beryllides with different microstructure. Fusion Engineering and Design, 2009, 84, 1136-1139. | 1.0 | 12 |
| 391 | Phase transitions in erbium-doped silicon exposed to laser radiation. Journal of Applied Spectroscopy, 2009, 76, 209-214. | 0.3 | 5 |
| 392 | Structural and photoluminescence studies of erbiumâ€implanted nanocrystalline silicon thin films. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2161-2165. | 0.8 | 0 |
| 393 | Electrical, structural and optical characterization of copper oxide thin films as a function of post annealing temperature. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2143-2148. | 0.8 | 67 |
| 394 | Temperature behavior of damage in sapphire implanted with light ions. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 1464-1467. | 0.6 | 4 |
| 395 | Lattice location and annealing studies of Hf implanted CaF2. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 1472-1475. | 0.6 | 1 |
| 396 | Radiation damage in ZnO ion implanted at 15K. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 2708-2711. | 0.6 | 64 |

| # | Article | IF | Citations |
|---|---|---|---|
| 397 | Stable In-defect complexes in GaN and AlN. Physica B: Condensed Matter, 2009, 404, 4866-4869. | 1.3 | 4 |
| 398 | Role of impurities and dislocations for the unintentional n-type conductivity in InN. Physica B: Condensed Matter, 2009, 404, 4476-4481. | 1.3 | 15 |
| 399 | The role of composition, morphology and crystalline structure in the electrochemical behaviour of TiNx thin films for dry electrode sensor materials. Electrochimica Acta, 2009, 55, 59-67. | 2.6 | 40 |
| 400 | Structural and electrical properties of Al doped ZnO thin films deposited at room temperature on poly(vinilidene fluoride) substrates. Thin Solid Films, 2009, 517, 6290-6293. | 0.8 | 24 |
| 401 | Compositional analysis and evolution of defects formed on GaInP epilayers grown on Germanium. Superlattices and Microstructures, 2009, 45, 277-284. | 1.4 | 14 |
| 402 | Ion beam processing of sapphire single crystals. Surface and Coatings Technology, 2009, 203, 2357-2362. | 2.2 | 9 |
| 403 | Structural evolution of Tiâ€“Alâ€“Siâ€“N nanocomposite coatings. Vacuum, 2009, 83, 1206-1212. | 1.6 | 36 |
| 404 | Adhesion failures on hard coatings induced by interface anomalies. Vacuum, 2009, 83, 1213-1217. | 1.6 | 18 |
| 405 | Structural and optical properties of nitrogen doped ZnO films. Vacuum, 2009, 83, 1274-1278. | 1.6 | 11 |
| 406 | Influence of the AlN molar fraction on the structural and optical properties of praseodymium-doped AlxGa1â^'xN (0â©½xâ©½1) alloys. Microelectronics Journal, 2009, 40, 377-380. | 1.1 | 15 |
| 407 | Structural and optical properties on thulium-doped LHPG-grown Ta2O5 fibres. Microelectronics Journal, 2009, 40, 309-312. | 1.1 | 10 |
| 408 | Microstructural evolution in tungsten and copper probes under hydrogen irradiation at ISTTOK. Journal of Nuclear Materials, 2009, 390-391, 1039-1042. | 1.3 | 7 |
| 409 | Comparison of the damage in sapphire due to implantation of boron, nitrogen, and iron. Journal of Nuclear Materials, 2009, 389, 311-316. | 1.3 | 6 |
| 410 | Morphological and optical properties of silicon thin films by PLD. Applied Surface Science, 2009, 255, 5299-5302. | 3.1 | 9 |
| 411 | Photosensitivity of nanocrystalline ZnO films grown by PLD. Applied Surface Science, 2009, 255, 5917-5921. | 3.1 | 9 |
| 412 | New Approaches to Thermoelectric Materials. NATO Science for Peace and Security Series B: Physics and Biophysics, 2009, , 51-67. | 0.2 | 5 |
| 413 | Features of the pulsed treatment of silicon layers implanted with erbium ions. Journal of Surface Investigation, 2009, 3, 604-607. | 0.1 | 2 |
| 414 | Annealing Ni nanocrystalline on WCâ€“Co. Journal of Alloys and Compounds, 2009, 482, 131-136. | 2.8 | 2 |

| # | Article | IF | Citations |
|---|---|---|---|
| 415 | Free electron behavior in InN: On the role of dislocations and surface electron accumulation. Applied Physics Letters, 2009, 94, 022109. | 1.5 | 41 |
| 416 | ZrO<sub>x</sub>N<sub>y</sub>decorative thin films prepared by the reactive gas pulsing process. Journal Physics D: Applied Physics, 2009, 42, 195501. | 1.3 | 24 |
| 417 | Electrical properties of solâ€“gel derived MPB 0.37BiScO3â€“0.63PbTiO3 thin films deposited on iridium oxide electrodes. Journal of Materials Chemistry, 2009, 19, 5572. | 6.7 | 7 |
| 418 | Ion Beam Analysis of Iridium-Based TES for Microcalorimeter Detectors. , 2009, , . | | 0 |
| 419 | ZnO Thin Films Implanted with Al, Sb and P: Optical, Structural and Electrical Characterization. Journal of Nanoscience and Nanotechnology, 2009, 9, 3574-3577. | 0.9 | 2 |
| 420 | Box 6: Nanoscale Defects. Particle Acceleration and Detection, 2009, , 205-210. | 0.3 | 0 |
| 421 | Elemental and RBS analysis of hybrid materials prepared by gamma-irradiation. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 288-294. | 0.6 | 6 |
| 422 | RBS analysis of InGaN/GaN quantum wells for hybrid structures with efficient FÃ¶rster coupling. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1402-1406. | 0.6 | 2 |
| 423 | Determination of non-Rutherford cross-sections from simple RBS spectra using Bayesian inference data analysis. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1180-1184. | 0.6 | 12 |
| 424 | Defect studies on fast and thermal neutron irradiated GaN. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 2780-2783. | 0.6 | 20 |
| 425 | Anisotropy effects on the formation of new phases in Î±-Al2O3 by high fluence Zn implantation. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 3129-3132. | 0.6 | 1 |
| 426 | Mechanisms of AlInN growth by MOVPE: modeling and experimental study. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1688-1690. | 0.8 | 8 |
| 427 | Luminescence and vibrational properties of erbium-implanted nanoporous GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1753-1755. | 0.8 | 0 |
| 428 | A comparative investigation of the damage buildâ€up in GaN and Si during rare earth ion implantation. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 68-70. | 0.8 | 3 |
| 429 | Rare earth doping of IIIâ€nitride alloys by ion implantation. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 34-37. | 0.8 | 8 |
| 430 | Role of the oxygen partial pressure on the properties of undoped tin oxide films deposited at low temperature. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1957-1960. | 0.8 | 1 |
| 431 | Luminescence spectroscopy of Euâ€implanted zincblende GaN. Physica Status Solidi (B): Basic Research, 2008, 245, 170-173. | 0.7 | 3 |
| 432 | Relaxation of compressively strained AlInN on GaN. Journal of Crystal Growth, 2008, 310, 4058-4064. | 0.7 | 50 |

| # | Article | IF | Citations |
|---|---|---|---|
| 433 | Comparison of ZnO thin films grown by pulsed laser deposition on sapphire and Si substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 699-704. | 1.3 | 19 |
| 434 | A comparative structural investigation of GaN implanted with rare earth ions at room temperature and 500Â°C. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 204-207. | 1.7 | 9 |
| 435 | Effect of post-annealing on the properties of copper oxide thin films obtained from the oxidation of evaporated metallic copper. Applied Surface Science, 2008, 254, 3949-3954. | 3.1 | 226 |
| 436 | Memory effect on CdSe nanocrystals embedded in SiO2 matrix. Solid State Communications, 2008, 148, 105-108. | 0.9 | 11 |
| 437 | Influence of air oxidation on the properties of decorative NbOxNy coatings prepared by reactive gas pulsing. Surface and Coatings Technology, 2008, 202, 2363-2367. | 2.2 | 16 |
| 438 | Effect of thermal treatments on the structure of MoNxOy thin films. Vacuum, 2008, 82, 1428-1432. | 1.6 | 18 |
| 439 | Raman and XRD studies of Ge nanocrystals in alumina films grown by RF-magnetron sputtering. Vacuum, 2008, 82, 1466-1469. | 1.6 | 25 |
| 440 | PVD-Grown photocatalytic TiO2 thin films on PVDF substrates for sensors and actuators applications. Thin Solid Films, 2008, 517, 1161-1166. | 0.8 | 48 |
| 441 | Electronic properties of Ge islands embedded in multilayer and superlattice structures. Thin Solid Films, 2008, 517, 303-305. | 0.8 | 2 |
| 442 | Radiation hardness of GeSi heterostructures with thin Ge layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 147, 191-194. | 1.7 | 7 |
| 443 | Ion beam studies of InAs/GaAs self assembled quantum dots. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1439-1442. | 0.6 | 0 |
| 444 | Electrical conductivity in undoped Î±-Al2O3 crystals implanted with Mg ions. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 2932-2935. | 0.6 | 6 |
| 445 | Structural study of the oxidation process and stability of NbOxNy coatings. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 4927-4932. | 0.6 | 1 |
| 446 | Charging effects in CdSe nanocrystals embedded in SiO2 matrix produced by rf magnetron sputtering. Microelectronic Engineering, 2008, 85, 2374-2377. | 1.1 | 11 |
| 447 | Visible and infrared luminescence study of Er doped Î²-Ga<sub>2</sub>O<sub>3</sub>and Er<sub>3</sub>Ga<sub>5</sub>O<sub>12</sub>. Journal Physics D: Applied Physics, 2008, 41, 065406. | 1.3 | 29 |
| 448 | Influence of the chemical and electronic structure on the electrical behavior of zirconium oxynitride films. Journal of Applied Physics, 2008, 103, . | 1.1 | 66 |
| 449 | Microwave dielectric permittivity and photoluminescence of Eu2O3 doped laser heated pedestal growth Ta2O5 fibers. Applied Physics Letters, 2008, 92, 252904. | 1.5 | 6 |
| 450 | Two colour experiments in Eu3+ implanted GaN. Journal of Alloys and Compounds, 2008, 451, 140-142. | 2.8 | 6 |

| # | Article | IF | Citations |
|---|---|---|---|
| 451 | Evaluation of exposure parameters in plain radiography: a comparative study with European guidelines. Radiation Protection Dosimetry, 2008, 129, 316-320. | 0.4 | 7 |
| 452 | Co-doping of aluminium and gallium with nitrogen in ZnO films deposited by RF magnetron sputtering. Journal of Physics Condensed Matter, 2008, 20, 075220. | 0.7 | 7 |
| 453 | Effects of hydrogen permeation on W, Mo and Cu Langmuir probes at ISTTOK. Materials Research Society Symposia Proceedings, 2008, 1125, 1. | 0.1 | 0 |
| 454 | Microstructure characterization of ODS-RAFM steels. Materials Research Society Symposia Proceedings, 2008, 1125, 1. | 0.1 | 0 |
| 455 | W-Diamond/Cu-Diamond nanostructured composites for fusion devices. Materials Research Society Symposia Proceedings, 2008, 1125, 1. | 0.1 | 1 |
| 456 | Optical energies of AlInN epilayers. Journal of Applied Physics, 2008, 103, . | 1.1 | 58 |
| 457 | Further insight into the temperature quenching of photoluminescence from InAsâˆ•GaAs self-assembled quantum dots. Journal of Applied Physics, 2008, 103, . | 1.1 | 22 |
| 458 | Enhancement of Erbium Incorporation with Implantation into Nanoporous GaN. , 2008, , . | | 0 |
| 459 | Temperature dependence of the electric field gradient in GaN measured with the PAC-probe 181Hf. , 2008, , 217-223. | | 0 |
| 460 | OPTICAL AND STRUCTURAL ANALYSIS OF Ge/Si QUANTUM DOTS GROWN ON A Si(001) SURFACE COVERED WITH A SiO2 SUB-MONOLAYER. International Journal of Nanoscience, 2007, 06, 245-248. | 0.4 | 0 |
| 461 | Metal-organic vapor phase epitaxy and properties of AlInN in the whole compositional range. Applied Physics Letters, 2007, 90, 022105. | 1.5 | 119 |
| 462 | Arsenic in ZnO and GaN: Substitutional Cation or Anion Sites?. Materials Research Society Symposia Proceedings, 2007, 994, 1. | 0.1 | 2 |
| 463 | Structural and Oxidation Studies of Titanium Beryllides. Nuclear Technology, 2007, 159, 233-237. | 0.7 | 2 |
| 464 | Tribological behaviour of Cl-implanted TiN coatings for biomedical applications. Wear, 2007, 262, 1337-1345. | 1.5 | 28 |
| 465 | Efficient dipole-dipole coupling of Mott-Wannier and Frenkel excitons in (Ga,In)N quantum well/polyfluorene semiconductor heterostructures. Physical Review B, 2007, 76, . | 1.1 | 64 |
| 466 | Stability of GaN films under intense MeV He ion irradiation. Diamond and Related Materials, 2007, 16, 1437-1440. | 1.8 | 3 |
| 467 | Structural and optical properties of Er3+ion in solâ€“gel grown LiNbO3. Journal of Physics Condensed Matter, 2007, 19, 016213. | 0.7 | 8 |
| 468 | Role of Nanoscale Strain Inhomogeneity on the Light Emission from InGaN Epilayers. Advanced Functional Materials, 2007, 17, 37-42. | 7.8 | 60 |

| # | Article | IF | Citations |
|---|---|---|---|
| 469 | Lattice location of implanted As in ZnO. Superlattices and Microstructures, 2007, 42, 8-13. | 1.4 | 4 |
| 470 | Optical and structural behaviour of Cu-implanted sapphire. Surface and Coatings Technology, 2007, 201, 8190-8196. | 2.2 | 9 |
| 471 | Influence of the O/C ratio in the behaviour of TiCxOy thin films. Surface and Coatings Technology, 2007, 201, 5587-5591. | 2.2 | 28 |
| 472 | Dual DC magnetron cathode co-deposition of (Al,Ti) and (Al,Ti,N) thin films with controlled depth composition. Vacuum, 2007, 81, 1503-1506. | 1.6 | 4 |
| 473 | Microstructural studies and electrical properties of Mg-doped SrTiO3 thin films. Acta Materialia, 2007, 55, 4947-4954. | 3.8 | 9 |
| 474 | Influence of the solâ€“gel growth parameters on the optical and structural properties on LiNbO3 samples. Materials Science and Engineering C, 2007, 27, 1065-1068. | 3.8 | 4 |
| 475 | Structural and optical characterisation of Eu implanted AlxGa1â^'xN. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 307-310. | 0.6 | 10 |
| 476 | Implantation of nanoporous GaN with Eu ions. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 328-331. | 0.6 | 2 |
| 477 | Synthesis of ZnO nanocrystals in sapphire by ion implantation and vacuum annealing. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 515-518. | 0.6 | 14 |
| 478 | Lithium ion implantation and annealing of MgO single crystals. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 558-562. | 0.6 | 1 |
| 479 | Copper and cobalt nanocolloids in implanted MgO crystals. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 563-567. | 0.6 | 7 |
| 480 | Spectroscopic investigation of implanted epilayers of Tm3+:GaN. Journal of Luminescence, 2007, 122-123, 131-133. | 1.5 | 3 |
| 481 | Radiation-induced structural transformations in a silicon layer of SOI. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 2645-2650. | 0.8 | 1 |
| 482 | Relaxation behaviour of Co and Ni implanted into MgO. Journal of Magnetism and Magnetic Materials, 2007, 316, e776-e778. | 1.0 | 6 |
| 483 | Anisotropic ferromagnetism induced in rutile single crystals by Co implantation. European Physical Journal B, 2007, 55, 253-260. | 0.6 | 15 |
| 484 | Optical studies of ZnO nanocrystals doped with Eu3+ ions. Applied Physics A: Materials Science and Processing, 2007, 88, 129-133. | 1.1 | 53 |
| 485 | Temperature dependence of the electric field gradient in GaN measured with the PAC-probe 181Hf. Hyperfine Interactions, 2007, 177, 89-95. | 0.2 | 5 |
| 486 | Holistic RBSâ€“PIXE data reanalysis of SBT thin film samples. Nuclear Instruments & Methods in Physics Research B, 2007, 261, 439-442. | 0.6 | 11 |

| # | Article | IF | Citations |
|---|---|---|---|
| 487 | Ion implantation and ion beam analysis of MOD deposited oxide films. Nuclear Instruments & Methods in Physics Research B, 2007, 261, 456-460. | 0.6 | 0 |
| 488 | Synthesis, surface modification and optical properties of Tb3+-doped ZnO nanocrystals. Nanotechnology, 2006, 17, 834-839. | 1.3 | 75 |
| 489 | Anomalous Ion Channeling inAlInN/GaNBilayers: Determination of the Strain State. Physical Review Letters, 2006, 97, 085501. | 2.9 | 125 |
| 490 | Study of the oxygen role in the photoluminescence of erbium doped nanocrystalline silicon embedded in a silicon amorphous matrix. Journal of Non-Crystalline Solids, 2006, 352, 1148-1151. | 1.5 | 2 |
| 491 | Optical active centres in ZnO samples. Journal of Non-Crystalline Solids, 2006, 352, 1453-1456. | 1.5 | 18 |
| 492 | Radiation-induced defects in a-Si:H by 1.5MeV He4 particles studied by photoconductivity and photothermal deflection spectroscopy. Journal of Non-Crystalline Solids, 2006, 352, 1071-1074. | 1.5 | 6 |
| 493 | Hydrogenated silicon carbon nitride films obtained by HWCVD, PA-HWCVD and PECVD techniques. Journal of Non-Crystalline Solids, 2006, 352, 1361-1366. | 1.5 | 45 |
| 494 | Transparent thin film transistors based on indium oxide semiconductor. Journal of Non-Crystalline Solids, 2006, 352, 2311-2314. | 1.5 | 48 |
| 495 | Optical properties of Er3++ Yb3+doped gallium nitride layers. , 2006, , . | | 0 |
| 496 | Luminescence and structural properties of defects in ion implanted ZnO. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 968-971. | 0.8 | 9 |
| 497 | Investigations of p-type signal for ZnO thin films grown on (100) GaAs substrates by pulsed laser deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1038-1041. | 0.8 | 16 |
| 498 | Depth profiling of ion-implanted AlInN using time-of-flight secondary ion mass spectrometry and cathodoluminescence. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1927-1930. | 0.8 | 8 |
| 499 | Behaviour of the AlN cap during GaN implantation of rare earths and annealing. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2172-2175. | 0.8 | 8 |
| 500 | Structure and role of ultrathin AlN layers for improving optical activation of rare earth implanted GaN. Physica Status Solidi (B): Basic Research, 2006, 243, 1541-1544. | 0.7 | 1 |
| 501 | Investigation of the nonlinear optical characteristics of composite materials based on sapphire with silver, copper, and gold nanoparticles by the reflection Z-scan method. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2006, 101, 615-622. | 0.2 | 11 |
| 502 | Microstructural studies of PZT thick films on Cu foils. Acta Materialia, 2006, 54, 3211-3220. | 3.8 | 24 |
| 503 | Optical doping of AlN by rare earth implantation. Nuclear Instruments & Methods in Physics Research B, 2006, 242, 307-310. | 0.6 | 23 |
| 504 | Optical properties tailoring by high fluence implantation of Ag ions on sapphire. Nuclear Instruments & Methods in Physics Research B, 2006, 242, 104-108. | 0.6 | 9 |

| # | Article | IF | Citations |
|---|---|---|---|
| 505 | Stability and luminescence studies of Tm and Er implanted ZnO single crystals. Nuclear Instruments & Methods in Physics Research B, 2006, 242, 580-584. | 0.6 | 25 |
| 506 | Accurate simulation of backscattering spectra in the presence of sharp resonances. Nuclear Instruments & Methods in Physics Research B, 2006, 247, 381-389. | 0.6 | 23 |
| 507 | Compositional and structural changes in ZrOxNy films depending on growth condition. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 458-461. | 0.6 | 8 |
| 508 | RBS/channeling study of buried Ge quantum dots grown in a Si layer. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 462-465. | 0.6 | 5 |
| 509 | Ion beam characterisation of ODS steel samples after long term annealing conditions. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 493-496. | 0.6 | 6 |
| 510 | RBS and XRD analysis of SiGe/Ge heterostructures for p-HMOS applications. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 878-881. | 0.6 | 0 |
| 511 | Defect production in neutron irradiated GaN. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 358-361. | 0.6 | 27 |
| 512 | Structure and optical properties of sapphire implanted with boron at room temperature and 1000Â°C. Nuclear Instruments & Methods in Physics Research B, 2006, 250, 81-84. | 0.6 | 3 |
| 513 | Optical and structural behaviour of Mn implanted sapphire. Nuclear Instruments & Methods in Physics Research B, 2006, 250, 90-94. | 0.6 | 1 |
| 514 | TEM investigation of Tm implanted GaN, the influence of high temperature annealing. Optical Materials, 2006, 28, 738-741. | 1.7 | 16 |
| 515 | High temperature annealing of rare earth implanted GaN films: Structural and optical properties. Optical Materials, 2006, 28, 750-758. | 1.7 | 47 |
| 516 | Lattice order in thulium-doped GaN epilayers: In situ doping versus ion implantation. Optical Materials, 2006, 28, 771-774. | 1.7 | 6 |
| 517 | Effect of annealing temperature on luminescence in Eu implanted GaN. Optical Materials, 2006, 28, 780-784. | 1.7 | 29 |
| 518 | Influence of defects on the optical and structural properties of Ge dots embedded in an Si/Ge superlattice. Journal of Luminescence, 2006, 121, 417-420. | 1.5 | 11 |
| 519 | Simulation of deep resonances in elastic backscattering data. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 796-799. | 0.6 | 2 |
| 520 | Analysis of solâ€“gel silicaâ€“titania films doped with Ag and Er using artificial neural networks. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 804-807. | 0.6 | 3 |
| 521 | Damage behaviour of GaAs/AlAs multilayer structures. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 890-893. | 0.6 | 1 |
| 522 | Optical behaviour of Er doped rutile by ion implantation. Nuclear Instruments & Methods in Physics Research B, 2006, 250, 363-367. | 0.6 | 4 |

| # | Article | IF | Citations |
|---|---|---|---|
| 523 | Lattice sites of implanted Cu and Ag in ZnO. Superlattices and Microstructures, 2006, 39, 229-237. | 1.4 | 20 |
| 524 | The structure of crystallographic damage in GaN formed during rare earth ion implantation with and without an ultrathin AlN capping layer. Superlattices and Microstructures, 2006, 40, 300-305. | 1.4 | 4 |
| 525 | Blue cathodoluminescence from thulium implanted AlxGa1â^'xN and InxAl1â^'xN. Superlattices and Microstructures, 2006, 40, 445-451. | 1.4 | 10 |
| 526 | Optical studies on a coherent InGaN/GaN layer. Superlattices and Microstructures, 2006, 40, 452-457. | 1.4 | 2 |
| 527 | Structural evolution in ZrNxOy thin films as a function of temperature. Surface and Coatings Technology, 2006, 200, 2917-2922. | 2.2 | 46 |
| 528 | Tribocorrosion behaviour of ZrOxNy thin films for decorative applications. Surface and Coatings Technology, 2006, 200, 6634-6639. | 2.2 | 32 |
| 529 | Diffusion processes in seeded and unseeded SBT thin films with varied stoichiometry. Surface Science, 2006, 600, 1780-1786. | 0.8 | 11 |
| 530 | Properties of MoNxOy thin films as a function of the N/O ratio. Thin Solid Films, 2006, 494, 201-206. | 0.8 | 22 |
| 531 | Ion synthesis and optical properties of gold nanoparticles in an Al2O3 matrix. Technical Physics, 2006, 51, 1474-1481. | 0.2 | 10 |
| 532 | Optical properties of high-temperature annealed Eu-implanted GaN. Optical Materials, 2006, 28, 797-801. | 1.7 | 8 |
| 533 | Optical and structural analysis of bulk ZnO samples undoped and rare earth doped by ion implantation. Superlattices and Microstructures, 2006, 39, 202-210. | 1.4 | 25 |
| 534 | UV-Raman scattering study of lattice recovery by thermal annealing of Eu+ -implanted GaN layers. Superlattices and Microstructures, 2006, 40, 440-444. | 1.4 | 1 |
| 535 | Optical and structural studies in Eu-implanted AlN films. Superlattices and Microstructures, 2006, 40, 537-544. | 1.4 | 14 |
| 536 | Raman spectra and structural analysis in ZrOxNy thin films. Thin Solid Films, 2006, 515, 1132-1137. | 0.8 | 38 |
| 537 | Phase Separation on GaInAsSb Films for Thermophotovoltaic Devices. Materials Science Forum, 2006, 514-516, 447-451. | 0.3 | 1 |
| 538 | Structural and Optical Characterization of Light Emitting InGaN/GaN Epitaxial Layers. Materials Science Forum, 2006, 514-516, 38-42. | 0.3 | 3 |
| 539 | Characterization of Nickel Implanted Î±-Al<sub>2</sub>O<sub>3</sub>. Materials Science Forum, 2006, 514-516, 348-352. | 0.3 | 0 |
| 540 | X-Ray Diffraction Study of Ordered Antiferromagnets for Tunnel Junctions. Materials Science Forum, 2006, 514-516, 314-318. | 0.3 | 0 |

| # | Article | IF | Citations |
|---|---|---|---|
| 541 | Ion Beam Analysis of Ge/Si Dots Grown on Ultrathin SiO<sub>2</sub> Interlayers. Materials Science Forum, 2006, 514-516, 1121-1124. | 0.3 | 0 |
| 542 | Hardware and Software Improvements in the Hotbird. Materials Science Forum, 2006, 514-516, 1678-1681. | 0.3 | 1 |
| 543 | Phase Transformation and Structural Studies of EUROFER RAFM Alloy. Materials Science Forum, 2006, 514-516, 500-504. | 0.3 | 19 |
| 544 | Effect of the Matrix on the 1.5Î¼m Photoluminescence of Er-Doped Silicon Quantum Dots. Materials Science Forum, 2006, 514-516, 1116-1120. | 0.3 | 1 |
| 545 | Combination of IBA Techniques for Composition Analysis of GaInAsSb Films. Materials Science Forum, 2006, 514-516, 1603-1607. | 0.3 | 5 |
| 546 | Influence of Rapid Thermal Annealing on the Luminescence Properties of Nanoporous GaN Films. Electrochemical and Solid-State Letters, 2006, 9, G150. | 2.2 | 11 |
| 547 | Identification of donor-related impurities in ZnO using photoluminescence and radiotracer techniques. Physical Review B, 2006, 73, . | 1.1 | 59 |
| 548 | Optical activation of Eu ions in nanoporous GaN films. Journal of Applied Physics, 2006, 99, 104305. | 1.1 | 6 |
| 549 | Cathodoluminescence of rare earth implanted AlInN. Applied Physics Letters, 2006, 89, 131912. | 1.5 | 15 |
| 550 | Failure mechanism of AlN nanocaps used to protect rare earth-implanted GaN during high temperature annealing. Applied Physics Letters, 2006, 88, 031902. | 1.5 | 18 |
| 551 | Transmission electron microscopy investigation of the structural damage formed in GaN by medium range energy rare earth ion implantation. Journal of Applied Physics, 2006, 100, 073520. | 1.1 | 58 |
| 552 | Rare Earth Ion Implantation in GaN: Damage Formation and Recovery. Acta Physica Polonica A, 2006, 110, 125-137. | 0.2 | 3 |
| 553 | Characterization of the blue emission of Tm/Er co-implanted GaN. Materials Research Society Symposia Proceedings, 2005, 892, 544. | 0.1 | 3 |
| 554 | Structural and composition analysis of GaN films deposited by cyclic-PLD at different substrate temperatures. Sensors and Actuators A: Physical, 2005, 121, 131-135. | 2.0 | 4 |
| 555 | XRD analysis of strained Geâ€“SiGe heterostructures on relaxed SiGe graded buffers grown by hybrid epitaxy on Si(001) substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 123-126. | 1.7 | 4 |
| 556 | Stability of erbium and silver implanted in silicaâ€“titania solâ€“gel films. Nuclear Instruments & Methods in Physics Research B, 2005, 240, 415-419. | 0.6 | 4 |
| 557 | Rutherford backscattering and X-ray reflectivity analysis of tunnel barriers. Nuclear Instruments & Methods in Physics Research B, 2005, 240, 365-370. | 0.6 | 1 |
| 558 | Analysis of nanolayered samples with a 4He beam. Nuclear Instruments & Methods in Physics Research B, 2005, 241, 361-364. | 0.6 | 0 |

| # | Article | IF | Citations |
|---|---|---|---|
| 559 | Application of RZ-scan technique for investigation of nonlinear refraction of sapphire doped with Ag, Cu, and Au nanoparticles. Optics Communications, 2005, 253, 205-213. | 1.0 | 58 |
| 560 | Microstructural characterization of Eurofer-ODS RAFM steel in the normalized and tempered condition and after thermal aging in simulated fusion conditions. Fusion Engineering and Design, 2005, 75-79, 1061-1065. | 1.0 | 21 |
| 561 | Optical and structural study of Ge/Si quantum dots on Si(100) surface covered with a thin silicon oxide layer. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 462-465. | 1.7 | 6 |
| 562 | Compositional and structural characterisation of GaSb and GaInSb. Nuclear Instruments & Methods in Physics Research B, 2005, 240, 360-364. | 0.6 | 3 |
| 563 | Site location and optical properties of Eu implanted sapphire. Nuclear Instruments & Methods in Physics Research B, 2005, 240, 409-414. | 0.6 | 0 |
| 564 | Beyond single scattering off flat samples. Nuclear Instruments & Methods in Physics Research B, 2005, 241, 316-320. | 0.6 | 4 |
| 565 | Ion beam analysis of GaInAsSb films grown by MOVPE on GaSb. Nuclear Instruments & Methods in Physics Research B, 2005, 241, 326-330. | 0.6 | 6 |
| 566 | High resolution backscattering studies of nanostructured magnetic and semiconducting materials. Nuclear Instruments & Methods in Physics Research B, 2005, 241, 454-458. | 0.6 | 13 |
| 567 | Characterization of silicon carbide thin films and their use in colour sensor. Solar Energy Materials and Solar Cells, 2005, 87, 343-348. | 3.0 | 2 |
| 568 | Influence of nitrogen content on the structural, mechanical and electrical properties of TiN thin films. Surface and Coatings Technology, 2005, 191, 317-323. | 2.2 | 146 |
| 569 | Structural stability of decorative ZrNxOy thin films. Surface and Coatings Technology, 2005, 200, 748-752. | 2.2 | 27 |
| 570 | Magnetic nanoscale aggregates of cobalt and nickel in MgO single crystals. European Physical Journal B, 2005, 45, 331-338. | 0.6 | 15 |
| 571 | Nonlinear optical properties of gold nanoparticles synthesized by ion implantation in sapphire matrix. Technical Physics Letters, 2005, 31, 702-705. | 0.2 | 21 |
| 572 | Magnetic properties of TiO2 rutile implanted with Ni and Co. Journal of Magnetism and Magnetic Materials, 2005, 294, e73-e76. | 1.0 | 20 |
| 573 | Characterization and stability studies of titanium beryllides. Fusion Engineering and Design, 2005, 75-79, 759-763. | 1.0 | 2 |
| 574 | The atomic structure of defects formed during doping of GaN with rare earth ions. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1081-1084. | 0.8 | 5 |
| 575 | Detection angle resolved PIXE and the equivalent depth concept for thin film characterization. X-Ray Spectrometry, 2005, 34, 372-375. | 0.9 | 23 |
| 576 | Influence of the Annealing Ambient on Structural and Optical Properties of Rare Earth Implanted GaN. Materials Research Society Symposia Proceedings, 2005, 892, 556. | 0.1 | 2 |

| # | Article | IF | Citations |
|---|---|---|---|
| 577 | Annealing properties of ZnO films grown using diethyl zinc and tertiary butanol. Journal of Physics Condensed Matter, 2005, 17, 1719-1724. | 0.7 | 16 |
| 578 | Comment on â€œDirect evidence of nanocluster-induced luminescence in InGaN epifilmsâ€•[Appl. Phys. Lett. 86, 021911 (2005)]. Applied Physics Letters, 2005, 87, 136101. | 1.5 | 3 |
| 579 | Up conversion from visible to ultraviolet in bulk ZnO implanted with Tm ions. Applied Physics Letters, 2005, 87, 192108. | 1.5 | 25 |
| 580 | Damage formation and annealing at low temperatures in ion implanted ZnO. Applied Physics Letters, 2005, 87, 191904. | 1.5 | 100 |
| 581 | Selectively excited photoluminescence from Eu-implanted GaN. Applied Physics Letters, 2005, 87, 112107. | 1.5 | 85 |
| 582 | Direct Evidence for As as a Zn-Site Impurity in ZnO. Physical Review Letters, 2005, 95, 215503. | 2.9 | 86 |
| 583 | A microspectroscopic study of cap damage in annealed RE-doped AlN-capped GaN. Materials Research Society Symposia Proceedings, 2005, 892, 568. | 0.1 | 0 |
| 584 | A green-emitting CdSe/poly(butyl acrylate) nanocomposite. Nanotechnology, 2005, 16, 1969-1973. | 1.3 | 25 |
| 585 | Near-band-edge slow luminescence in nominally undoped bulk ZnO. Journal of Applied Physics, 2005, 98, 013502. | 1.1 | 54 |
| 586 | Structural, electrical, optical, and mechanical characterizations of decorative ZrOxNy thin films. Journal of Applied Physics, 2005, 98, 023715. | 1.1 | 87 |
| 587 | Recent Emission Channeling Studies in Wide Band Gap Semiconductors. , 2005, , 792-801. | | 0 |
| 588 | PAC Studies of Implanted 111Ag in Single-Crystalline ZnO. , 2005, , 395-400. | | 0 |
| 589 | Lattice location and stability of implanted Cu in ZnO. Physical Review B, 2004, 69, . | 1.1 | 40 |
| 590 | Exchange bias of MnPt/CoFe films prepared by ion beam deposition. Journal of Applied Physics, 2004, 95, 6317-6321. | 1.1 | 16 |
| 591 | Direct evidence for strain inhomogeneity in InxGa1â^'xN epilayers by Raman spectroscopy. Applied Physics Letters, 2004, 85, 2235-2237. | 1.5 | 21 |
| 592 | Influence of O and C co-implantation on the lattice site of Er in GaN. Applied Physics Letters, 2004, 84, 4304-4306. | 1.5 | 15 |
| 593 | Optical and mechanical properties of MgO crystals implanted with lithium ions. Journal of Applied Physics, 2004, 95, 2371-2378. | 1.1 | 7 |
| 594 | High-temperature annealing and optical activation of Eu-implanted GaN. Applied Physics Letters, 2004, 85, 2712-2714. | 1.5 | 67 |

| # | Article | IF | Citations |
|---|---|---|---|
| 595 | The role of microstructure in luminescent properties of Er-doped nanocrystalline Si thin films. Physics of the Solid State, 2004, 46, 113-117. | 0.2 | 2 |
| 596 | Roughness in GaN/InGaN films and multilayers determined with Rutherford backscattering. Nuclear Instruments & Methods in Physics Research B, 2004, 217, 479-497. | 0.6 | 30 |
| 597 | Optical changes induced by high fluence implantation of Au ions on sapphire. Nuclear Instruments & Methods in Physics Research B, 2004, 218, 139-144. | 0.6 | 15 |
| 598 | Stability and optical activity of Er implanted MgO. Nuclear Instruments & Methods in Physics Research B, 2004, 218, 128-132. | 0.6 | 1 |
| 599 | Defect production in nitrogen implanted sapphire. Nuclear Instruments & Methods in Physics Research B, 2004, 218, 222-226. | 0.6 | 6 |
| 600 | Comparative study of radiation damage in GaN and InGaN by 400 keV Au implantation. Nuclear Instruments & Methods in Physics Research B, 2004, 218, 36-41. | 0.6 | 28 |
| 601 | Copper nanocolloids in MgO crystals implanted with Cu ions. Nuclear Instruments & Methods in Physics Research B, 2004, 218, 148-152. | 0.6 | 7 |
| 602 | Electrical conductivity of as-grown and oxidized MgO:Li crystals implanted with Li ions. Nuclear Instruments & Methods in Physics Research B, 2004, 218, 164-169. | 0.6 | 6 |
| 603 | The effect of temperature on the structure of iron-implanted sapphire. Nuclear Instruments & Methods in Physics Research B, 2004, 218, 227-231. | 0.6 | 5 |
| 604 | Characterization of FePt nanoparticles in FePt/C multilayers. Nuclear Instruments & Methods in Physics Research B, 2004, 219-220, 919-922. | 0.6 | 4 |
| 605 | Study of silicaâ€“titania films doped with Er and Ag by RBS and ERDA. Nuclear Instruments & Methods in Physics Research B, 2004, 219-220, 923-927. | 0.6 | 5 |
| 606 | RBS analysis of AlGaSb thin films. Nuclear Instruments & Methods in Physics Research B, 2004, 219-220, 928-932. | 0.6 | 1 |
| 607 | Ion beam studies of single crystalline manganite thin films. Nuclear Instruments & Methods in Physics Research B, 2004, 219-220, 933-937. | 0.6 | 0 |
| 608 | Structural, optical and mechanical properties of coloured TiNxOy thin films. Thin Solid Films, 2004, 447-448, 449-454. | 0.8 | 169 |
| 609 | Compositional Profiles in Silica-Based Sol-Gel Films Doped with Erbium and Silver, by RBS and ERDA. Journal of Sol-Gel Science and Technology, 2004, 31, 287-291. | 1.1 | 7 |
| 610 | Amorphisation of GaN during processing with rare earth ion beams. Superlattices and Microstructures, 2004, 36, 737-745. | 1.4 | 27 |
| 611 | PAC Studies of Implanted 111Ag in Single-Crystalline ZnO. Hyperfine Interactions, 2004, 158, 395-400. | 0.2 | 9 |
| 612 | Recent Emission Channeling Studies in Wide Band Gap Semiconductors. Hyperfine Interactions, 2004, 159, 363-372. | 0.2 | 9 |

| # | Article | IF | Citations |
|---|---|---|---|
| 613 | Optical and RBS studies in Tm implanted ZnO samples. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 254-256. | 0.8 | 9 |
| 614 | Property change in ZrNxOy thin films: effect of the oxygen fraction and bias voltage. Thin Solid Films, 2004, 469-470, 11-17. | 0.8 | 65 |
| 615 | Corrosion resistance of ZrNxOy thin films obtained by rf reactive magnetron sputtering. Thin Solid Films, 2004, 469-470, 274-281. | 0.8 | 52 |
| 616 | Optical studies on the red luminescence of InGaN epilayers. Superlattices and Microstructures, 2004, 36, 625-632. | 1.4 | 8 |
| 617 | Characterisation of defects in rare earth implanted GaN by deep level transient spectroscopy. Superlattices and Microstructures, 2004, 36, 713-719. | 1.4 | 6 |
| 618 | Extended X-ray absorption fine structure studies of thulium doped GaN epilayers. Superlattices and Microstructures, 2004, 36, 729-736. | 1.4 | 9 |
| 619 | PL studies on ZnO single crystals implanted with thulium ions. Superlattices and Microstructures, 2004, 36, 747-753. | 1.4 | 14 |
| 620 | Microstructure of (Ti,Si,Al)N nanocomposite coatings. Surface and Coatings Technology, 2004, 177-178, 369-375. | 2.2 | 52 |
| 621 | Structural and corrosion behaviour of stoichiometric and substoichiometric TiN thin films. Surface and Coatings Technology, 2004, 180-181, 158-163. | 2.2 | 38 |
| 622 | Ion beam studies of TiNxOy thin films deposited by reactive magnetron sputtering. Surface and Coatings Technology, 2004, 180-181, 372-376. | 2.2 | 36 |
| 623 | Atomic environment and interfacial structural order of TiAlN/Mo multilayers. Surface and Coatings Technology, 2004, 187, 393-398. | 2.2 | 10 |
| 624 | Characterization of hard DC-sputtered Si-based TiN coatings: the effect of composition and ion bombardment. Surface and Coatings Technology, 2004, 188-189, 351-357. | 2.2 | 36 |
| 625 | Magnetic behavior of Co and Ni implanted MgO. Journal of Magnetism and Magnetic Materials, 2004, 272-276, 840-842. | 1.0 | 11 |
| 626 | Materials design data for reduced activation martensitic steel type EUROFER. Journal of Nuclear Materials, 2004, 329-333, 257-262. | 1.3 | 118 |
| 627 | Methods for the mitigation of the chemical reactivity of beryllium in steam. Journal of Nuclear Materials, 2004, 329-333, 1353-1356. | 1.3 | 1 |
| 628 | Li ceramic pebbles chemical compatibility with Eurofer samples in fusion relevant conditions. Journal of Nuclear Materials, 2004, 329-333, 1295-1299. | 1.3 | 9 |
| 629 | Lattice location and thermal stability of implanted Fe in ZnO. Applied Physics Letters, 2004, 85, 4899-4901. | 1.5 | 50 |
| 630 | Degradation of particle detectors based on a-Si:H by 1.5 Mev He4 and 1 MeV protons. Journal of Non-Crystalline Solids, 2004, 338-340, 814-817. | 1.5 | 4 |

| # | Article | IF | Citations |
|---|---|---|---|
| 631 | Formation of AlxGa1â^'xSb films over GaSb substrates by Al diffusion. EPJ Applied Physics, 2004, 27, 423-426. | 0.3 | 3 |
| 632 | Lattice site and stability of implanted Ag in ZnO. Physica B: Condensed Matter, 2003, 340-342, 240-244. | 1.3 | 23 |
| 633 | Lattice location and optical activation of rare earth implanted GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 132-140. | 1.7 | 44 |
| 634 | Structural and optical studies of Co and Ti implanted sapphire. Nuclear Instruments & Methods in Physics Research B, 2003, 207, 55-62. | 0.6 | 10 |
| 635 | Radiation-damage recovery in undoped and oxidized Li doped MgO crystals implanted with lithium ions. Nuclear Instruments & Methods in Physics Research B, 2003, 206, 148-152. | 0.6 | 6 |
| 636 | Three-step amorphisation process in ion-implanted GaN at 15 K. Nuclear Instruments & Methods in Physics Research B, 2003, 206, 1028-1032. | 0.6 | 71 |
| 637 | Annealing behavior and lattice site location of Er implanted InGaN. Nuclear Instruments & Methods in Physics Research B, 2003, 206, 1042-1046. | 0.6 | 3 |
| 638 | Lattice site location and optical activity of Er implanted ZnO. Nuclear Instruments & Methods in Physics Research B, 2003, 206, 1047-1051. | 0.6 | 66 |
| 639 | High temperature chemical compatibility between SiC composites and Be pebbles. Nuclear Instruments & Methods in Physics Research B, 2003, 210, 495-500. | 0.6 | 0 |
| 640 | Implantation and annealing studies of Tm-implanted GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 97-100. | 1.7 | 13 |
| 641 | Optical absorption of a Li-related impurity in ZnO. Physica B: Condensed Matter, 2003, 340-342, 225-229. | 1.3 | 10 |
| 642 | Optical doping of ZnO with Tm by ion implantation. Physica B: Condensed Matter, 2003, 340-342, 235-239. | 1.3 | 30 |
| 643 | Influence of crystals distribution on the photoluminescence properties of nanocrystalline silicon thin films. Microelectronics Journal, 2003, 34, 375-378. | 1.1 | 1 |
| 644 | Effects of the morphology and structure on the elastic behavior of (Ti,Si,Al)N nanocomposites. Surface and Coatings Technology, 2003, 174-175, 984-991. | 2.2 | 21 |
| 645 | Preparation of magnetron sputtered TiNxOy thin films. Surface and Coatings Technology, 2003, 174-175, 197-203. | 2.2 | 74 |
| 646 | Mechanical characterization of reactively magnetron-sputtered TiN films. Surface and Coatings Technology, 2003, 174-175, 375-382. | 2.2 | 44 |
| 647 | Structural characterisation of SiC/SiCf composites exposed to chemical interaction with Be at high temperature. Fusion Engineering and Design, 2003, 69, 221-226. | 1.0 | 0 |
| 648 | Influence of ionizing radiation on the electrical behavior of a Be pebble bed. Fusion Engineering and Design, 2003, 69, 253-256. | 1.0 | 1 |

| # | Article | IF | Citations |
|---|---|---|---|
| 649 | Interrelation between microstructure and optical properties of erbium-doped nanocrystalline thin films. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 414-419. | 1.3 | 7 |
| 650 | Magnetic characterization of U/Co multilayers. Physica Status Solidi A, 2003, 196, 153-156. | 1.7 | 2 |
| 651 | Degradation of Structural and Optical Properties of InGaN/GaN Multiple Quantum Wells with Increasing Number of Wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 302-306. | 0.8 | 4 |
| 652 | Analysis of Strain Depth Variations in an In0.19Ga0.81N Layer by Raman Spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 563-567. | 0.8 | 7 |
| 653 | Implantation site of rare earths in single-crystalline ZnO. Applied Physics Letters, 2003, 82, 1173-1175. | 1.5 | 55 |
| 654 | Dielectric function of nanocrystalline silicon with few nanometers (<3 nm) grain size. Applied Physics Letters, 2003, 82, 2993-2995. | 1.5 | 58 |
| 655 | Photoluminescence and damage recovery studies in Fe-implanted ZnO single crystals. Journal of Applied Physics, 2003, 93, 8995-9000. | 1.1 | 56 |
| 656 | The influence ofin situphotoexcitation on a defect structure generation in ArÂimplanted GaAs(001) crystals revealed by high-resolution x-ray diffraction and Rutherford backscattering spectroscopy. Journal Physics D: Applied Physics, 2003, 36, A143-A147. | 1.3 | 9 |
| 657 | Raman study of the A1(LO) phonon in relaxed and pseudomorphic InGaN epilayers. Applied Physics Letters, 2003, 83, 4761-4763. | 1.5 | 53 |
| 658 | Processing of rare earth doped GaN with ion beams. Materials Research Society Symposia Proceedings, 2003, 798, 569. | 0.1 | 5 |
| 659 | High Temperature Implantation of Tm in GaN. Materials Research Society Symposia Proceedings, 2003, 798, 548. | 0.1 | 6 |
| 660 | Electron micro-probe analysis and cathodoluminescence spectroscopy of rare earth - implanted GaN. Materials Research Society Symposia Proceedings, 2003, 798, 466. | 0.1 | 1 |
| 661 | Room-temperature growth of crystalline indium tin oxide films on glass using low-energy oxygen-ion-beam assisted deposition. Journal of Applied Physics, 2003, 93, 2262-2266. | 1.1 | 42 |
| 662 | Structural Development in Hard Si-Based TiN Coatings as a Function of Temperature: A Comprehensive Study in Vacuum and in Air. Materials Science Forum, 2002, 383, 151-160. | 0.3 | 2 |
| 663 | Optical activity and damage recovery of erbium implanted strontium titanate. Radiation Effects and Defects in Solids, 2002, 157, 1071-1076. | 0.4 | 5 |
| 664 | Depth profiling InGaN/GaN multiple quantum wells by Rutherford backscattering: The role of intermixing. Applied Physics Letters, 2002, 81, 2950-2952. | 1.5 | 15 |
| 665 | Mechanical and Adhesion Behaviours of Superhard (Ti,Si,Al)N Nanocomposite Films Grown by Reactive Magnetron Sputtering. Key Engineering Materials, 2002, 230-232, 185-188. | 0.4 | 0 |
| 666 | Lattice Site Location Studies of Rare-Earths Implanted in ZnO Single-Crystals. Materials Research Society Symposia Proceedings, 2002, 744, 1. | 0.1 | 0 |

| # | Article | IF | Citations |
|---|---|---|---|
| 667 | Structural and optical properties of InGaN/GaN layers close to the critical layer thickness. Applied Physics Letters, 2002, 81, 1207-1209. | 1.5 | 94 |
| 668 | Strain and composition distributions in wurtzite InGaN/GaN layers extracted from x-ray reciprocal space mapping. Applied Physics Letters, 2002, 80, 3913-3915. | 1.5 | 209 |
| 669 | Preliminary investigations of infrared Er-related photoluminescence in ion-implanted In0.07Ga0.93N. Applied Physics Letters, 2002, 80, 4504-4506. | 1.5 | 6 |
| 670 | Luminescence studies of Co implanted sapphires. Radiation Effects and Defects in Solids, 2002, 157, 1117-1122. | 0.4 | 1 |
| 671 | Ion beam studies of MBE grown GaN films on silicon substrates. Nuclear Instruments & Methods in Physics Research B, 2002, 188, 73-77. | 0.6 | 6 |
| 672 | Study of roughness in Ti0.4Al0.6N/Mo multilayer structures. Nuclear Instruments & Methods in Physics Research B, 2002, 188, 90-95. | 0.6 | 14 |
| 673 | Study of calcium implanted GaN. Nuclear Instruments & Methods in Physics Research B, 2002, 190, 625-629. | 0.6 | 5 |
| 674 | Strain relaxation and compositional analysis of InGaN/GaN layers by Rutherford backscattering. Nuclear Instruments & Methods in Physics Research B, 2002, 190, 560-564. | 0.6 | 10 |
| 675 | Analysis of sapphire implanted with different elements using artificial neural networks. Nuclear Instruments & Methods in Physics Research B, 2002, 190, 241-246. | 0.6 | 6 |
| 676 | Surface quality studies of high-Tc superconductors of the Hg-, Tl- and HgxTl1â^'x-families: RBS and resonant C and O backscattering studies. Nuclear Instruments & Methods in Physics Research B, 2002, 190, 673-678. | 0.6 | 1 |
| 677 | Physical and morphological characterization of reactively magnetron sputtered TiN films. Thin Solid Films, 2002, 420-421, 421-428. | 0.8 | 21 |
| 678 | Nanoindentation on MgO crystals implanted with lithium ions. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 154-157. | 0.6 | 5 |
| 679 | Conductivity behaviour of Cr implanted TiO2. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 158-162. | 0.6 | 23 |
| 680 | Electrical conductivity of MgO crystals implanted with lithium ions. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 191-195. | 0.6 | 22 |
| 681 | Effects of ion implantation on the thermoluminescent properties of natural colourless topaz. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 196-201. | 0.6 | 7 |
| 682 | Structural and optical characterization of topaz implanted with Fe and Co. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 312-316. | 0.6 | 11 |
| 683 | Erbium implantation in strontium titanate. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 317-322. | 0.6 | 5 |
| 684 | Lattice location and annealing behavior of Mn implanted GaN. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 544-548. | 0.6 | 20 |

| # | Article | IF | Citations |
|---|---|---|---|
| 685 | The structure of sapphire implanted with nitrogen at room temperature and 1000 Â°C. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 629-632. | 0.6 | 6 |
| 686 | Luminescence and structural studies of iron implanted Î±-Al2O3. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 638-643. | 0.6 | 25 |
| 687 | Influence of annealing atmosphere on the behavior of titanium implanted sapphire. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 644-648. | 0.6 | 7 |
| 688 | Splitting of X-ray diffraction and photoluminescence peaks in InGaN/GaN layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 163-167. | 1.7 | 20 |
| 689 | Effects of ion bombardment on properties of d.c. sputtered superhard (Ti, Si, Al)N nanocomposite coatings. Surface and Coatings Technology, 2002, 151-152, 515-520. | 2.2 | 81 |
| 690 | Optical changes induced by high fluence implantation of Co ions on sapphire. Surface and Coatings Technology, 2002, 158-159, 54-58. | 2.2 | 5 |
| 691 | Elemental characterisation of beryllium and electrical behaviour of their pebbles beds. Journal of Nuclear Materials, 2002, 307-311, 643-646. | 1.3 | 4 |
| 692 | Interpretation of double x-ray diffraction peaks from InGaN layers. Applied Physics Letters, 2001, 79, 1432-1434. | 1.5 | 55 |
| 693 | Microstructure and mechanical properties of nanocomposite (Ti,Si,Al)N coatings. Thin Solid Films, 2001, 398-399, 391-396. | 0.8 | 131 |
| 694 | Heavy ion implantation in GaN epilayers. Radiation Effects and Defects in Solids, 2001, 156, 267-272. | 0.4 | 1 |
| 695 | Elastic properties of (Ti,Al,Si)N nanocomposite films. Surface and Coatings Technology, 2001, 142-144, 110-116. | 2.2 | 45 |
| 696 | Photoluminescence and lattice location of Eu and Pr implanted GaN samples. Physica B: Condensed Matter, 2001, 308-310, 22-25. | 1.3 | 91 |
| 697 | Green and red emission in Ca implanted GaN samples. Physica B: Condensed Matter, 2001, 308-310, 42-46. | 1.3 | 5 |
| 698 | Spectroscopic ellipsometry study of the layer structure and impurity content in Er-doped nanocrystalline silicon thin films. Physica B: Condensed Matter, 2001, 308-310, 374-377. | 1.3 | 4 |
| 699 | Photoluminescence studies in ZnO samples. Physica B: Condensed Matter, 2001, 308-310, 985-988. | 1.3 | 84 |
| 700 | High temperature annealing of Er implanted GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 132-135. | 1.7 | 13 |
| 701 | Indium Distribution within InxGa1?xN Epitaxial Layers: A Combined Resonant Raman Scattering and Rutherford Backscattering Study. Physica Status Solidi (B): Basic Research, 2001, 228, 173-177. | 0.7 | 2 |
| 702 | Depth Resolved Studies of Indium Content and Strain in InGaN Layers. Physica Status Solidi (B): Basic Research, 2001, 228, 59-64. | 0.7 | 7 |

| # | Article | IF | Citations |
|---|---|---|---|
| 703 | Indium content determination related with structural and optical properties of InGaN layers. Journal of Crystal Growth, 2001, 230, 448-453. | 0.7 | 8 |
| 704 | Hyperfine Fields of 181Ta in UFe4Al8. Hyperfine Interactions, 2001, 136/137, 333-337. | 0.2 | 4 |
| 705 | Amorphization of GaN by ion implantation. Nuclear Instruments & Methods in Physics Research B, 2001, 178, 200-203. | 0.6 | 15 |
| 706 | Coherent amorphization of Ge/Si multilayers with ion beams. Nuclear Instruments & Methods in Physics Research B, 2001, 178, 279-282. | 0.6 | 2 |
| 707 | Artificial neural network analysis of RBS data of Er-implanted sapphire. Nuclear Instruments & Methods in Physics Research B, 2001, 175-177, 108-112. | 0.6 | 5 |
| 708 | Study of new surface structures created on sapphire by Co ion implantation. Nuclear Instruments & Methods in Physics Research B, 2001, 175-177, 500-504. | 0.6 | 7 |
| 709 | Study of Fe+ implanted GaN. Nuclear Instruments & Methods in Physics Research B, 2001, 175-177, 241-245. | 0.6 | 9 |
| 710 | Study of solid-state reactions of SiC/SiCf composites using microbeams. Nuclear Instruments & Methods in Physics Research B, 2001, 181, 377-381. | 0.6 | 1 |
| 711 | Cadmium addition to vacancy doped lanthanum manganites: from metallic to insulator behaviour. Journal of Magnetism and Magnetic Materials, 2001, 226-230, 797-799. | 1.0 | 5 |
| 712 | OPTICAL DOPING OF NITRIDES BY ION IMPLANTATION. Modern Physics Letters B, 2001, 15, 1281-1287. | 1.0 | 33 |
| 713 | Fe ion implantation in GaN: Damage, annealing, and lattice site location. Journal of Applied Physics, 2001, 90, 81-86. | 1.1 | 24 |
| 714 | Green, red and infrared Er-related emission in implanted GaN:Er and GaN:Er,O samples. Journal of Applied Physics, 2001, 89, 6183-6188. | 1.1 | 34 |
| 715 | Compositional pulling effects inInxGa1â^'xN/GaNlayers:â€ƒA combined depth-resolved cathodoluminescence and Rutherford backscattering/channeling study. Physical Review B, 2001, 64, . | 1.1 | 176 |
| 716 | Compositional dependence of the strain-free optical band gap in InxGa1â^'xN layers. Applied Physics Letters, 2001, 78, 2137-2139. | 1.5 | 104 |
| 717 | Influence of Temperature and Pressure on the Beryllium Pebbles Bed Electrical Resistivity. Fusion Science and Technology, 2000, 38, 320-325. | 0.6 | 6 |
| 718 | Strain and Compositional Analysis of InGaN/GaN Layers. Materials Research Society Symposia Proceedings, 2000, 639, 3521. | 0.1 | 3 |
| 719 | Raman spectroscopy studies in InGaN/GaN wurtzite epitaxial films. Materials Research Society Symposia Proceedings, 2000, 639, 6101. | 0.1 | 2 |
| 720 | Optical Characterization of AlGaN/GaN MQW's. Materials Research Society Symposia Proceedings, 2000, 639, 6211. | 0.1 | 0 |

| # | Article | IF | Citations |
|---|---|---|---|
| 721 | Surface studies of SiC/SiCf composites exposed to relevant fusion reactor conditions. Surface and Interface Analysis, 2000, 30, 98-100. | 0.8 | 6 |
| 722 | Luminescence studies in colour centres produced in natural topaz. Journal of Luminescence, 2000, 87-89, 583-585. | 1.5 | 6 |
| 723 | Structure determination of (Ti,Al)N/Mo multilayers. Thin Solid Films, 2000, 373, 287-292. | 0.8 | 3 |
| 724 | Characterisation of Ti1â^'xSixNy nanocomposite films. Surface and Coatings Technology, 2000, 133-134, 307-313. | 2.2 | 190 |
| 725 | Structural and magnetic studies of Fe-implanted Î±-Al2O3. Surface and Coatings Technology, 2000, 128-129, 434-439. | 2.2 | 23 |
| 726 | Hard nanocomposite Tiâ€“Siâ€“N coatings prepared by DC reactive magnetron sputtering. Surface and Coatings Technology, 2000, 133-134, 234-239. | 2.2 | 115 |
| 727 | Anisotropic transport properties of epitaxial La2/3Ca1/3MnO3 thin films with different growth orientations (invited). Journal of Magnetism and Magnetic Materials, 2000, 211, 1-8. | 1.0 | 11 |
| 728 | Effect of crystal orientation on defect production and optical activation of Er-implanted sapphire. Nuclear Instruments & Methods in Physics Research B, 2000, 166-167, 183-187. | 0.6 | 14 |
| 729 | Annealing behaviour of natural topaz implanted with W and Cr ions. Nuclear Instruments & Methods in Physics Research B, 2000, 166-167, 204-208. | 0.6 | 8 |
| 730 | Influence of oxygen ion implantation on the damage and annealing kinetics of iron-implanted sapphire. Nuclear Instruments & Methods in Physics Research B, 2000, 166-167, 188-192. | 0.6 | 7 |
| 731 | RBS/Channeling study of Er doped GaN films grown by MBE on Si substrates. Nuclear Instruments & Methods in Physics Research B, 2000, 161-163, 946-951. | 0.6 | 22 |
| 732 | Micron-scale analysis of SiC/SiCf composites using the new Lisbon nuclear microprobe. Nuclear Instruments & Methods in Physics Research B, 2000, 161-163, 334-338. | 0.6 | 65 |
| 733 | Molecular H2 and H3 energy loss measurements along the Si â€ˆ111â€‰ direction. Nuclear Instruments & Methods in Physics Research B, 2000, 161-163, 168-171. | 0.6 | 5 |
| 734 | A structural and mechanical analysis on PVD-grown (Ti,Al)N/Mo multilayers. Thin Solid Films, 2000, 377-378, 425-429. | 0.8 | 20 |
| 735 | Anisotropic electrical transport in epitaxial La2/3Ca1/3MnO3 thin films. Journal of Applied Physics, 2000, 87, 5570-5572. | 1.1 | 22 |
| 736 | Annealing behavior and lattice site location of Hf implanted GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 207-210. | 1.7 | 22 |
| 737 | Characterisation of YBaCuO-PrBaCuO Multilayers Grown by Pulsed Injection MO-CVD. Journal of Low Temperature Physics, 1999, 117, 657-661. | 0.6 | 0 |
| 738 | Stability studies of Hg implanted YBa2Cu3O6+x. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 244-248. | 0.6 | 3 |

| # | Article | IF | Citations |
|---|---|---|---|
| 739 | Lattice location and annealing behaviour of Pt and W implanted sapphire. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 226-230. | 0.6 | 4 |
| 740 | Ion beam and photoluminescence studies of Er and O implanted GaN. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 383-387. | 0.6 | 26 |
| 741 | Formation of coherent precipitates of platinum in sapphire. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 1049-1053. | 0.6 | 14 |
| 742 | Stability and diffusion of Hg implanted YBa2Cu3O6+x. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 807-812. | 0.6 | 3 |
| 743 | Effect of crystal orientation on damage accumulation and post-implantation annealing for iron implantation into sapphire. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 730-734. | 0.6 | 10 |
| 744 | Nuclear microbeam study of advanced materials for fusion reactor technology. Nuclear Instruments & Methods in Physics Research B, 1999, 158, 671-677. | 0.6 | 2 |
| 745 | Properties of epitaxial LaCaMnO laser ablated thin films on (1 0 0) and (1 1 0) SrTiO3 substrates. Journal of Magnetism and Magnetic Materials, 1999, 196-197, 495-497. | 1.0 | 6 |
| 746 | Ion beam studies of CdTe films epitaxially grown on Si, GaAs and sapphire substrates. Nuclear Instruments & Methods in Physics Research B, 1998, 136-138, 220-224. | 0.6 | 6 |
| 747 | Lattice site location of thulium and erbium implanted GaAs. Nuclear Instruments & Methods in Physics Research B, 1998, 136-138, 421-425. | 0.6 | 5 |
| 748 | Lattice site location and annealing behavior of W implanted TiO2. Nuclear Instruments & Methods in Physics Research B, 1998, 136-138, 442-446. | 0.6 | 8 |
| 749 | Solubility and damage annealing of Er implanted single crystalline Î±-Al2O3. Nuclear Instruments & Methods in Physics Research B, 1998, 139, 313-317. | 0.6 | 9 |
| 750 | Chemical effects on the amorphization of sapphire. Nuclear Instruments & Methods in Physics Research B, 1998, 141, 353-357. | 0.6 | 10 |
| 751 | Microscopic studies of radioactive Hg implanted in YBa 2Cu3O6 + x superconducting thin films. Journal of Magnetism and Magnetic Materials, 1998, 177-181, 511-512. | 1.0 | 4 |
| 752 | Radioactive Isotope Identifications of Au and Pt Photoluminescence Centres in Silicon. Physica Status Solidi (B): Basic Research, 1998, 210, 853-858. | 0.7 | 9 |
| 753 | RBS Lattice Site Location and Damage Recovery Studies In GaN. Materials Research Society Symposia Proceedings, 1998, 537, 1. | 0.1 | 0 |
| 754 | Substrate effect on CdTe layers grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 1997, 70, 1314-1316. | 1.5 | 30 |
| 755 | The Photoluminescence of Pt-Implanted Silicon. Materials Science Forum, 1997, 258-263, 473-478. | 0.3 | 5 |
| 756 | Lattice site and photoluminescence of erbium implanted in Î±â€“Al<sub>2</sub>O<sub>3</sub>. Journal of Materials Research, 1997, 12, 1401-1404. | 1.2 | 26 |

| # | Article | IF | Citations |
|---|---|---|---|
| 757 | Improving the Thermal Stability of Photoresist Films by Ion Beam Irradiation. Materials Research Society Symposia Proceedings, 1997, 504, 443. | 0.1 | 1 |
| 758 | Etching of amorphous Al2O3 produced by ion implantation. Nuclear Instruments & Methods in Physics Research B, 1997, 127-128, 596-598. | 0.6 | 21 |
| 759 | Microscopic studies of implanted 73As in diamond. Nuclear Instruments & Methods in Physics Research B, 1997, 127-128, 723-726. | 0.6 | 20 |
| 760 | Selective area vapor-phase epitaxy and structural properties of Hg1 â^' xCdxTe on sapphire. Journal of Crystal Growth, 1997, 179, 585-591. | 0.7 | 7 |
| 761 | Rutherford Backscattering and Photoluminescence Studies of Erbium Implanted GaAs. Materials Research Society Symposia Proceedings, 1996, 422, 173. | 0.1 | 0 |
| 762 | Radiation damage annealing of Hg implanted InP. Nuclear Instruments & Methods in Physics Research B, 1996, 120, 244-247. | 0.6 | 1 |
| 763 | Low temperature epitaxial regrowth of mercury implanted sapphire. Nuclear Instruments & Methods in Physics Research B, 1996, 120, 248-251. | 0.6 | 2 |
| 764 | Ion beam mixing of chromium or zirconium films with sapphire. Surface and Coatings Technology, 1996, 83, 151-155. | 2.2 | 5 |
| 765 | Structural properties of CdTe and Hg1 â^' xCdxTe epitaxial layers grown on sapphire substrates. Journal of Crystal Growth, 1996, 161, 195-200. | 0.7 | 11 |
| 766 | Laser-assisted recrystallization to improve the surface morphology of CdTe epitaxial layers. Semiconductor Science and Technology, 1996, 11, 248-251. | 1.0 | 11 |
| 767 | Structural properties of layers grown on CdTe substrates by liquid phase epitaxy. Semiconductor Science and Technology, 1996, 11, 542-547. | 1.0 | 6 |
| 768 | Incorporation and stability of erbium in sapphire by ion implantation. , 1996, , 429-432. | | 0 |
| 769 | Incorporation and stability of erbium in sapphire by ion implantation. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 429-432. | 0.6 | 28 |
| 770 | The substitutionality of hafnium in sapphire by ion implantation and low temperature annealing. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 602-605. | 0.6 | 4 |
| 771 | Hyperfine fields of mercury in singleâ€crystalline cobalt. Journal of Applied Physics, 1994, 76, 6906-6908. | 1.1 | 5 |
| 772 | The lattice site of Au in Be after 24 h 197mHg isotope implantation and decay. Nuclear Instruments & Methods in Physics Research B, 1994, 85, 457-461. | 0.6 | 1 |
| 773 | Lattice location of Er in GaAs and Al0.5Ga0.5As layers grown by MBE on (100) GaAs substrates. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 180-183. | 0.6 | 10 |
| 774 | Lattice Location and Photoluminescence of Er in GaAs and Al0.5Ga0.5As. Materials Research Society Symposia Proceedings, 1993, 301, 175. | 0.1 | 4 |

| # | Article | IF | Citations |
|---|---|---|---|
| 775 | Vacancy-acceptor complexes in germanium produced by ion implantation. Nuclear Instruments & Methods in Physics Research B, 1991, 59-60, 1049-1052. | 0.6 | 6 |
| 776 | Lattice site location and outdiffusion of mercury implanted in GaAs. Nuclear Instruments & Methods in Physics Research B, 1991, 59-60, 1090-1093. | 0.6 | 3 |
| 777 | Epitaxial regrowth and lattice location of indium implanted in arsenic-preamorphized silicon. Nuclear Instruments & Methods in Physics Research B, 1991, 55, 580-584. | 0.6 | 5 |
| 778 | Regrowth of indium-implanted (100), (110) and (111) silicon crystals studied with Rutherford backscattering and perturbed angular correlation techniques. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1989, 4, 189-195. | 1.7 | 2 |
| 779 | Lattice Location Studies on Hafnium, Thallium and Lead Implanted Magnesium Single Crystals. , 1984, , 74-82. | | 6 |
| 780 | Electrical conductivity in ion implanted TiO/sub 2/-single crystals. , 0, , . | | 1 |
| 781 | Structural and Mechanical Properties of AZOY Thin Films Deposited on Flexible Substrates. Materials Science Forum, 0, 587-588, 834-838. | 0.3 | 0 |
| 782 | Study of SiGe Alloys with Different Germanium Concentrations Implanted with Mn and As Ions. Materials Science Forum, 0, 587-588, 298-302. | 0.3 | 0 |
| 783 | Room Temperature Magnetic Response of Sputter Deposited TbDyFe Films as a Function of the Deposition Parameters. Journal of Nano Research, 0, 18-19, 235-239. | 0.8 | 3 |
| 784 | Wettability and Nanotribological Response of Silicon Surfaces Functionalized by Ion Implantation. Materials Science Forum, 0, 730-732, 257-262. | 0.3 | 1 |
| 785 | Surface Plasmon Resonance Effect on the Optical Properties of TiO<sub>2</sub> Doped by Noble Metals Nanoparticles. Journal of Nano Research, 0, 18-19, 177-185. | 0.8 | 8 |